

Like driving a car: acquiring quality SEM/FESEM images in different situations

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About me

Bangzhi Liu | Assistant Research Professor

Nanofabrication Laboratory, Materials Research Institute, Penn State University

- FESEMs, EDS, Thermal ALD, PEALD, PVD, Ellipsometry;
- Process development, training, and maintenance;
- Internal and external projects

Background

- Ph.D. in Materials Science and Engineering | Michigan State University
- B.S. in Applied Physics | Dalian University of Technology, Dalian, CN



Hometown and workplace

9,500 ft² cleanroom (Class 1000 / 100)



- 2 EBL
- 2 FESEM
- 8 Dry etchers
- 5 ALD
- 1 AFM
- 3 Evap
- 4 Sputter
- 1 PECVD
- 2 Contact aligner
- 1 Laser Writer
- 1 MLA
- 1 Nano Imprinter
- 2 Wafer Bonder
- 3 RTA
- 1 Ellipsometer
- 1 Profilometer

Dalian



Millennium Science Complex



Outline

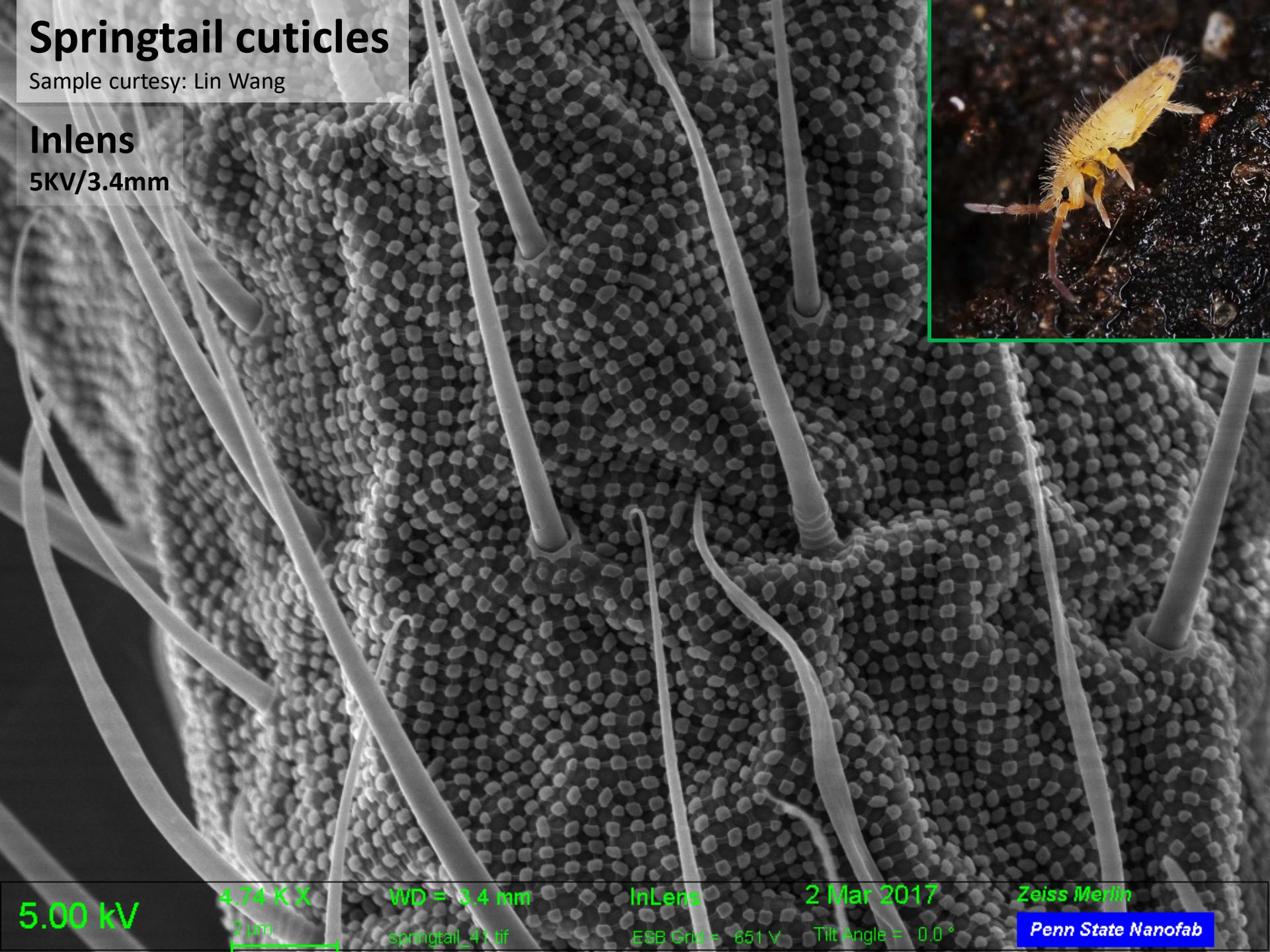
- Examples of different situations
- Key Imaging Parameters
- FESEMs we own
- How to achieve ideal beam

Springtail cuticles

Sample courtesy: Lin Wang

Inlens

5KV/3.4mm



5.00 kV

4.74 K X

2 μm

WD = 3.4 mm

Springtail_41.tif

InLens

ESB Grid = 651 V

2 Mar 2017

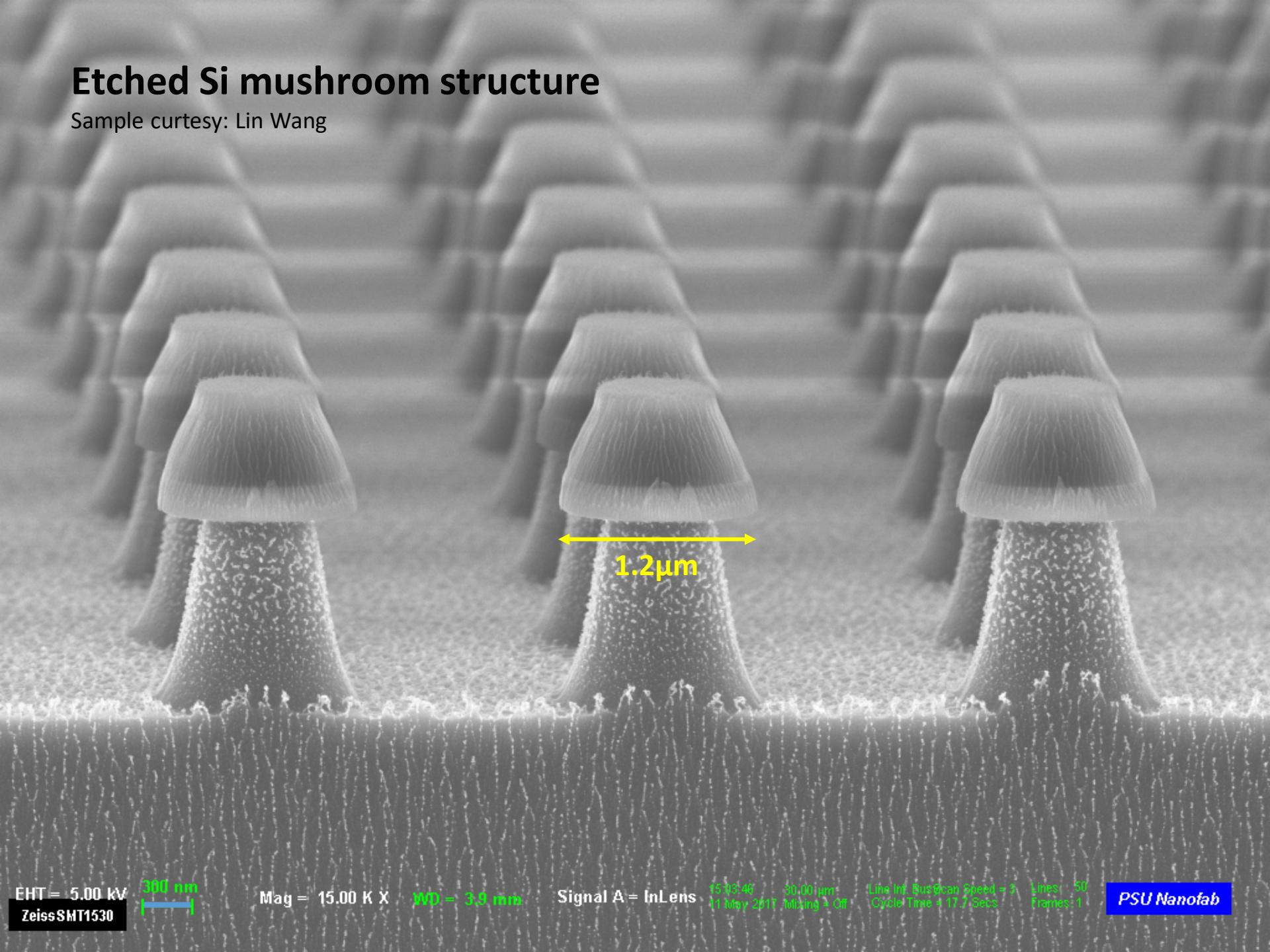
Tilt Angle = 0.0 °

Zeiss Merlin

Penn State Nanofab

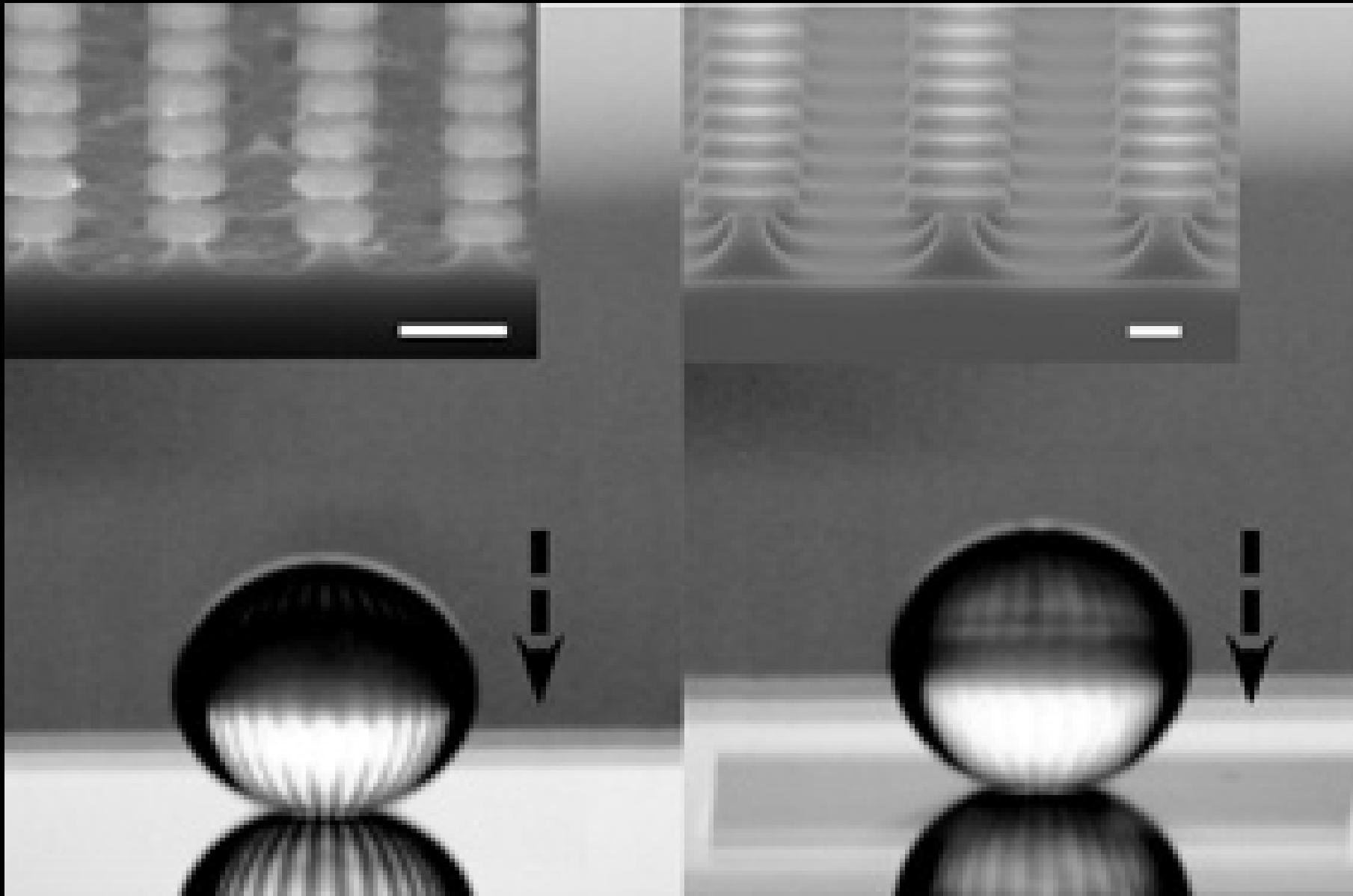
Etched Si mushroom structure

Sample courtesy: Lin Wang



EHT = 5.00 kV 300 nm Mag = 15.00 K X WD = 3.0 mm Signal A = InLens
Zeiss SMT1530 11:13:46 01 May 2011Y Mixing = 0.8 Line Int. Bus Read Speed = 3 Lines: 50
Cycle Time = 17.756ms Frame: 1

PSU Nanofab



Etched Si grating

Sample courtesy: Fabin Grise



EHT = 20.00 kV
Zeiss SMT1530

100 nm

Mag = 100.00 K XWD = 2.1 mm

Signal A = InLens

11:10:43
7 Oct 2016

30.00 μ m
Mixing = Off

Line Avg
Scan Speed = 3
Cycle Time = 17.7 Secs

Lines: 50
Frames: 5

PSU Nanofab

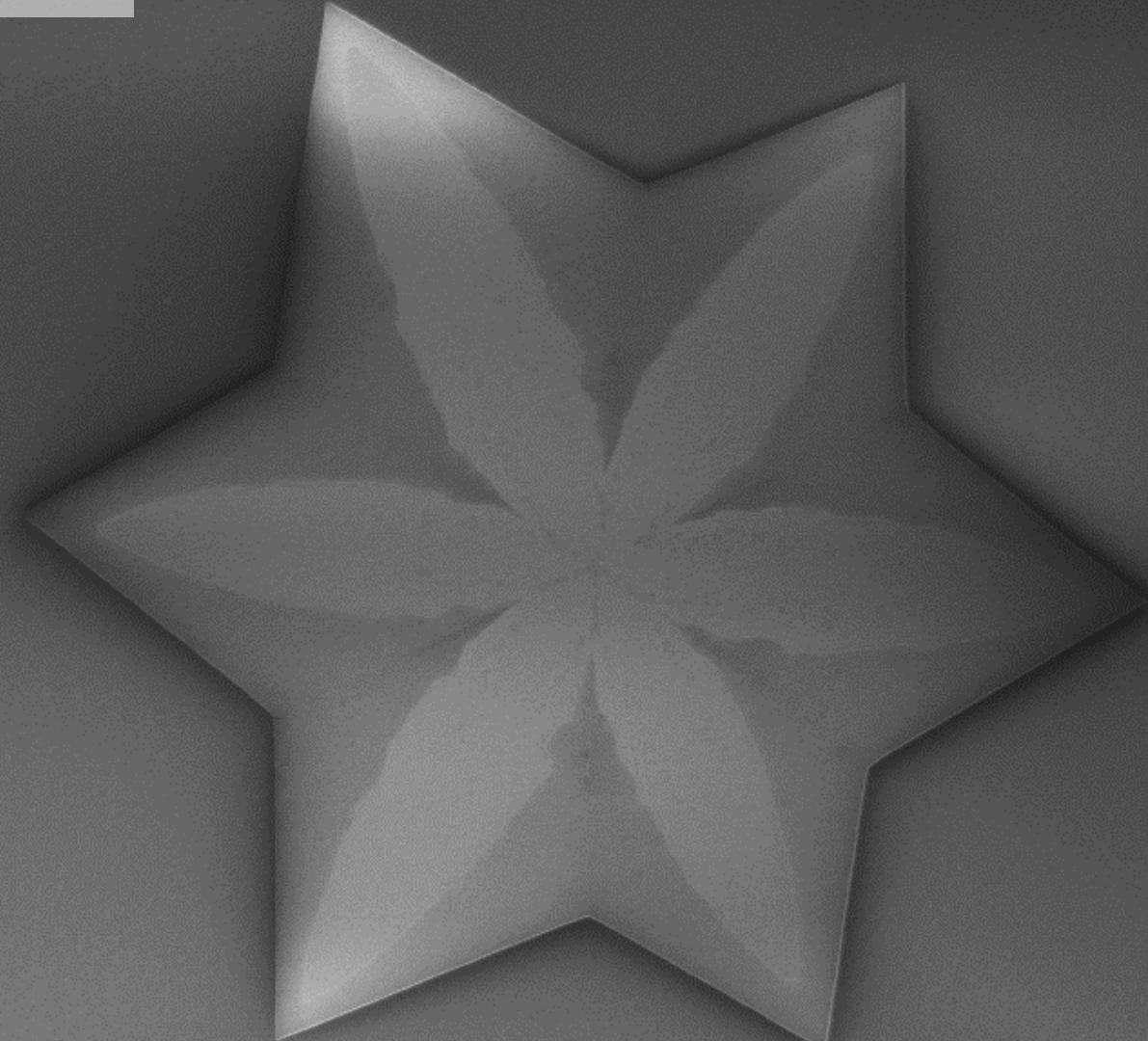
WSe₂/Graphene 0.2KV

Sample courtesy: Ben Huet

2um

MoS₂/0.2KV

Sample courtesy: Kevin Lu



10um

0.200 KV

1.69 KX

10 μm

WD = 2.7 mm

InLens

13 Nov 2019

Zeiss Gemini 500

1022_NWONMO_21.tif

15:49:29

Penn State Nanofab

3D printed nanostructure/2 kV

Sample curtesy: Jiho Noh

polymer

Glass substrate

2.00 kV

3.17 KX

2 μ m

WD = 4.6 mm

InLens

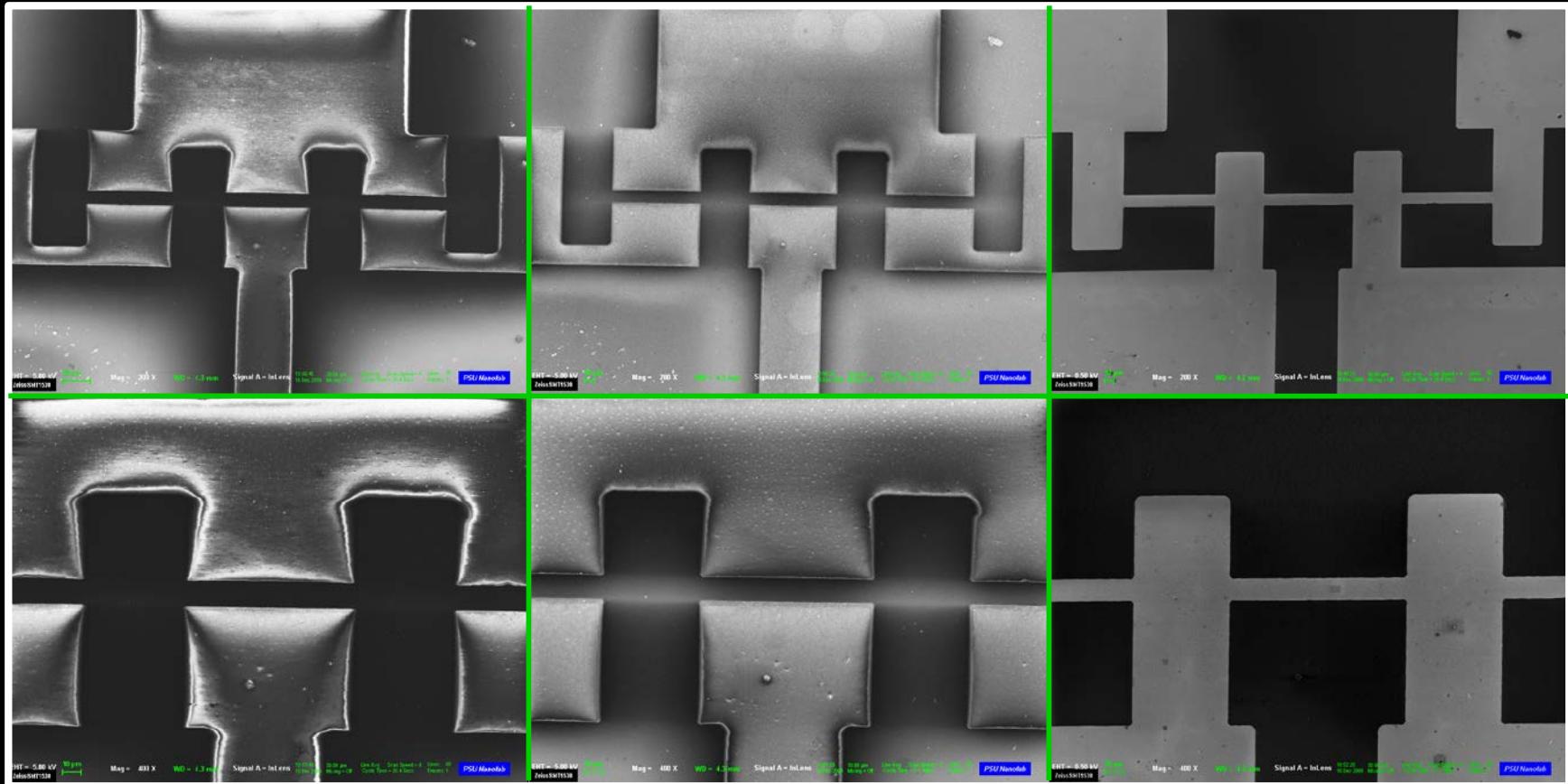
20 Apr 2018

Zeiss Merlin

ESB Grid = 1067 V

Penn State Nanofab

Charging effect



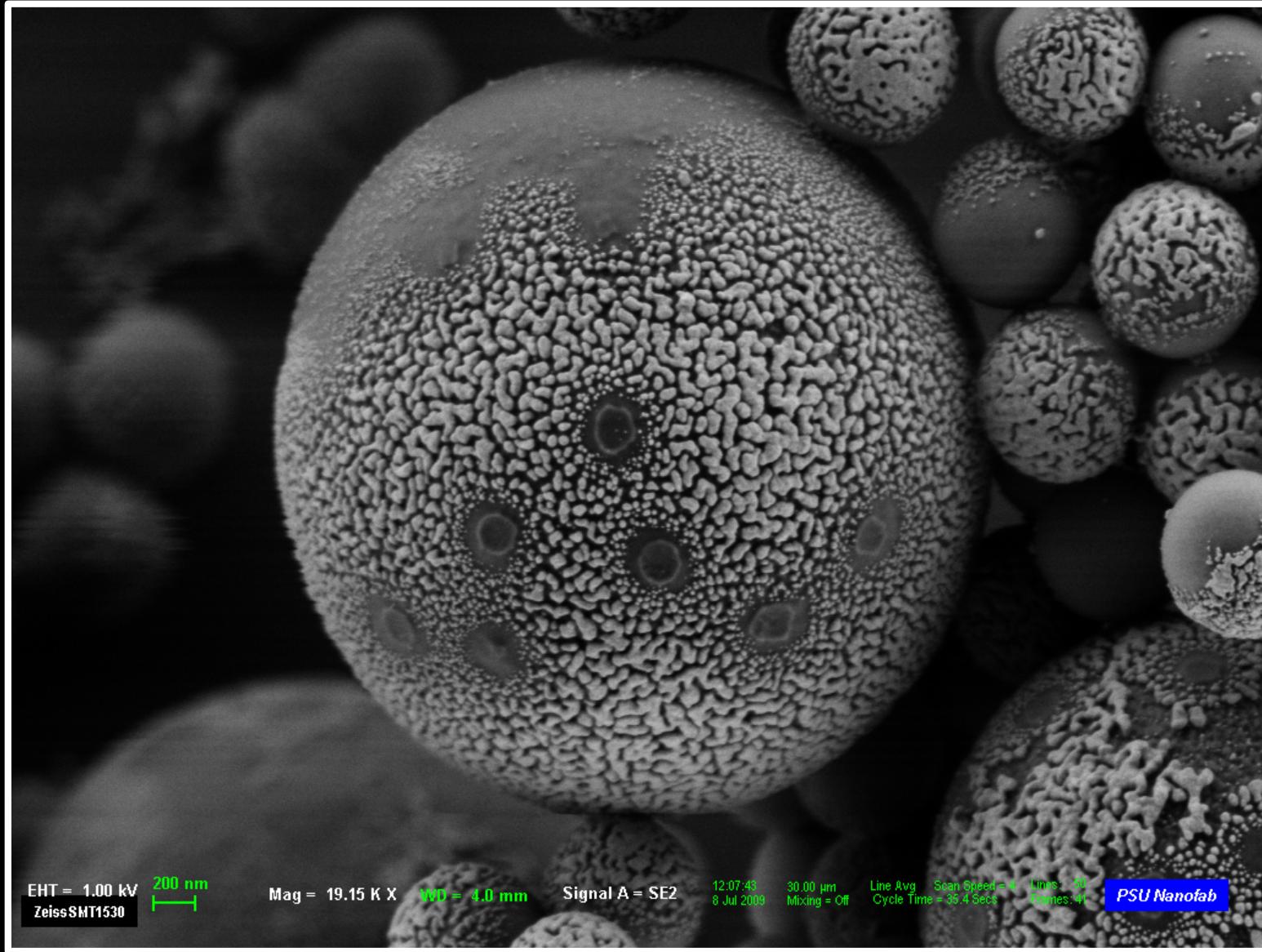
5 kV / 30 µm aperture

5 kV / 10 µm aperture

0.5 kV / 30 µm aperture

LEO1530

Polystyrene latex coated with Au





2.00 kV

100X

200 μ m

WD = 3.8 mm

SE2

ESB Grid = 333 V

1 Jun 2022

Tilt Angle = -2.9°

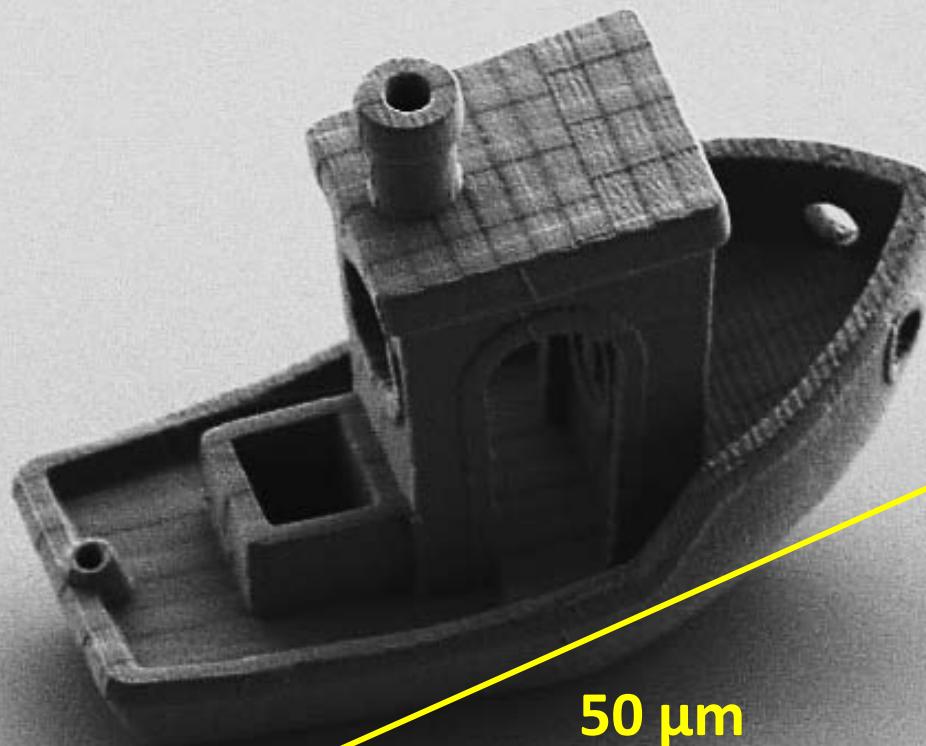
Zeiss Merlin

Penn State Nanofab

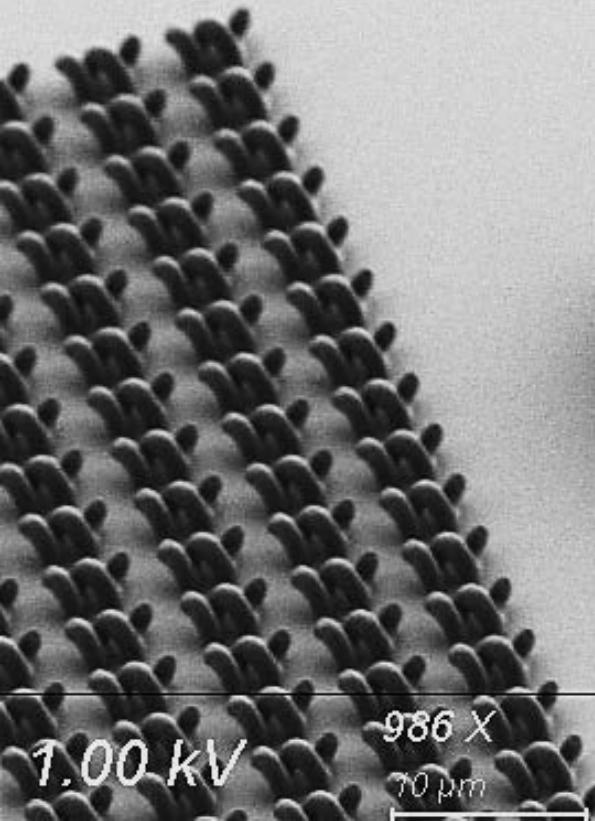
50 um 3D printed boat

SE2 1KV/7.1mm

Sample courtesy: Nicole Famularo



50 μm



1.00 KV

986 X

70 μm

WD = 7.1 mm

SE2

6 Jul 2018

ESB Gnd = 967 V

Tilt Angle = 0.0

Zeiss M

Penn S

Outline

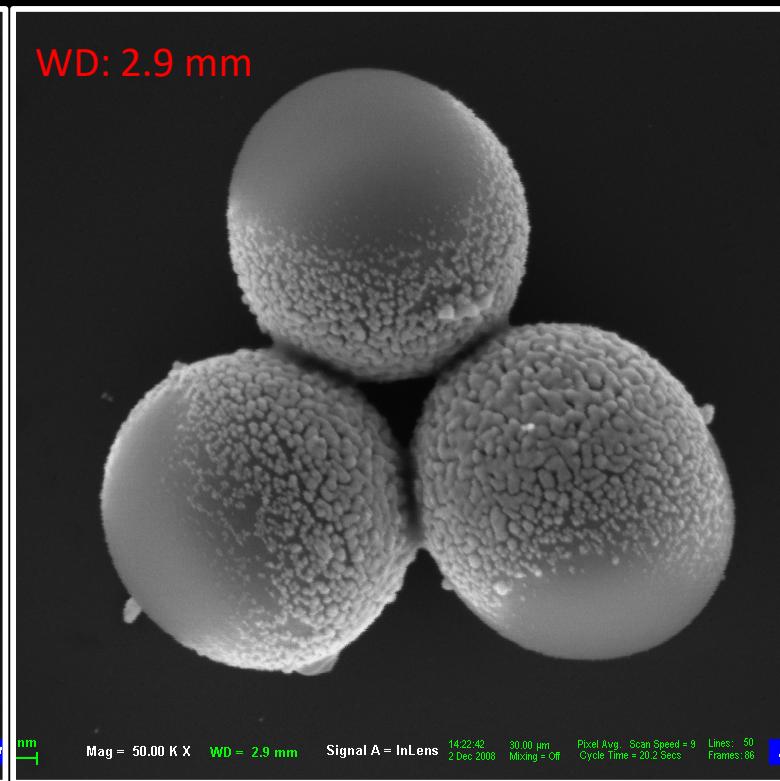
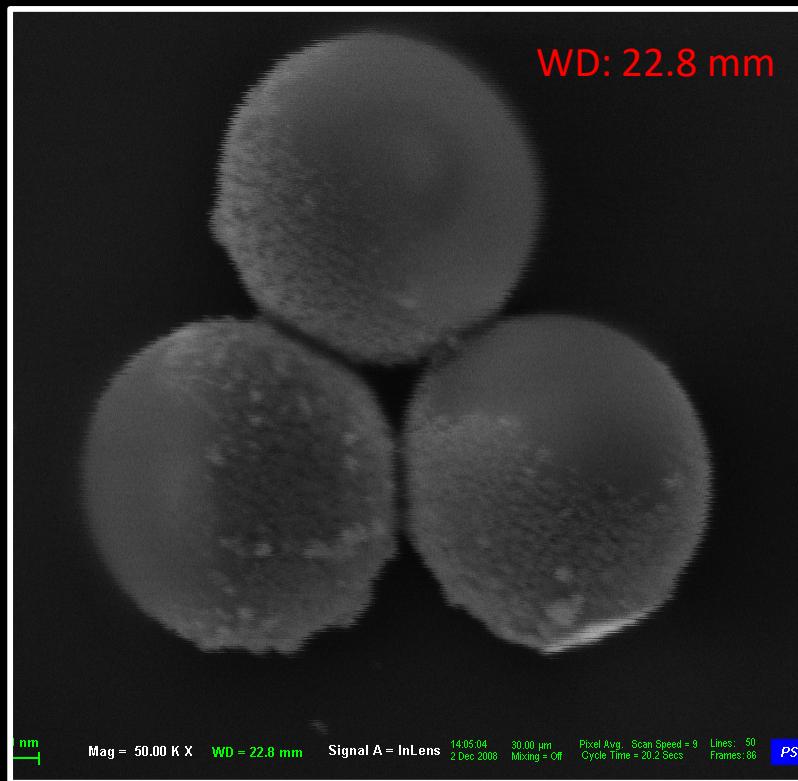
- Examples of different situations
- **Key Imaging Parameters**
- FESEMs we own
- How to achieve ideal beam

Key imaging parameters

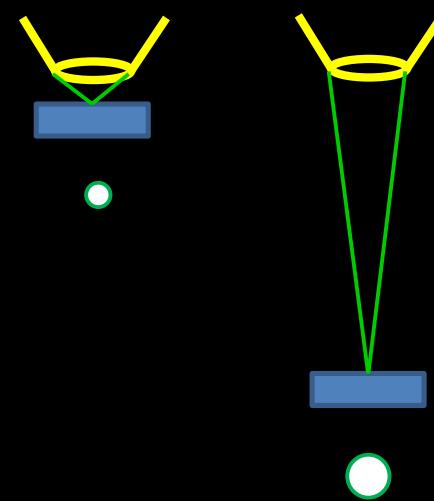
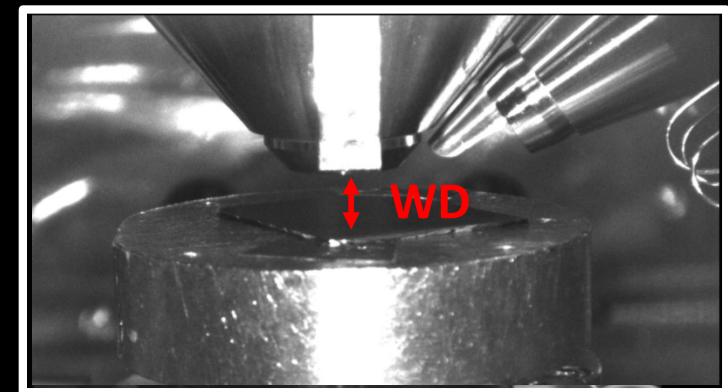
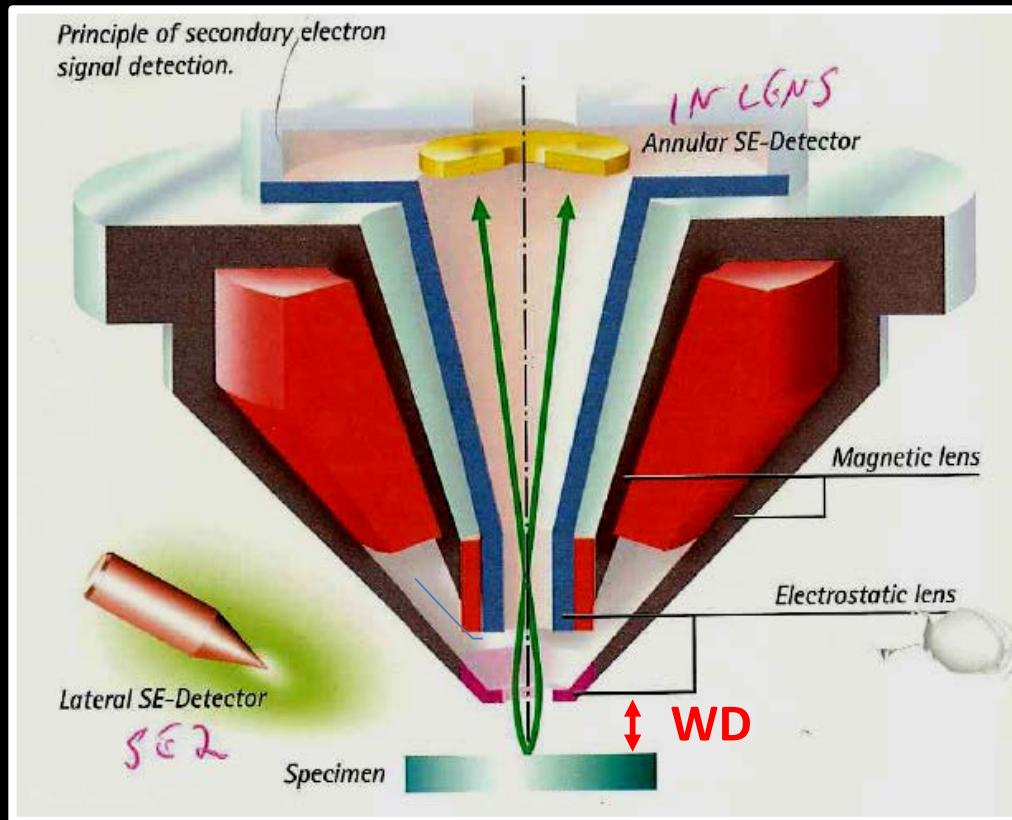
- **Working distance (WD)**
- **Beam voltage**
- **Detectors**

Working Distance (WD)

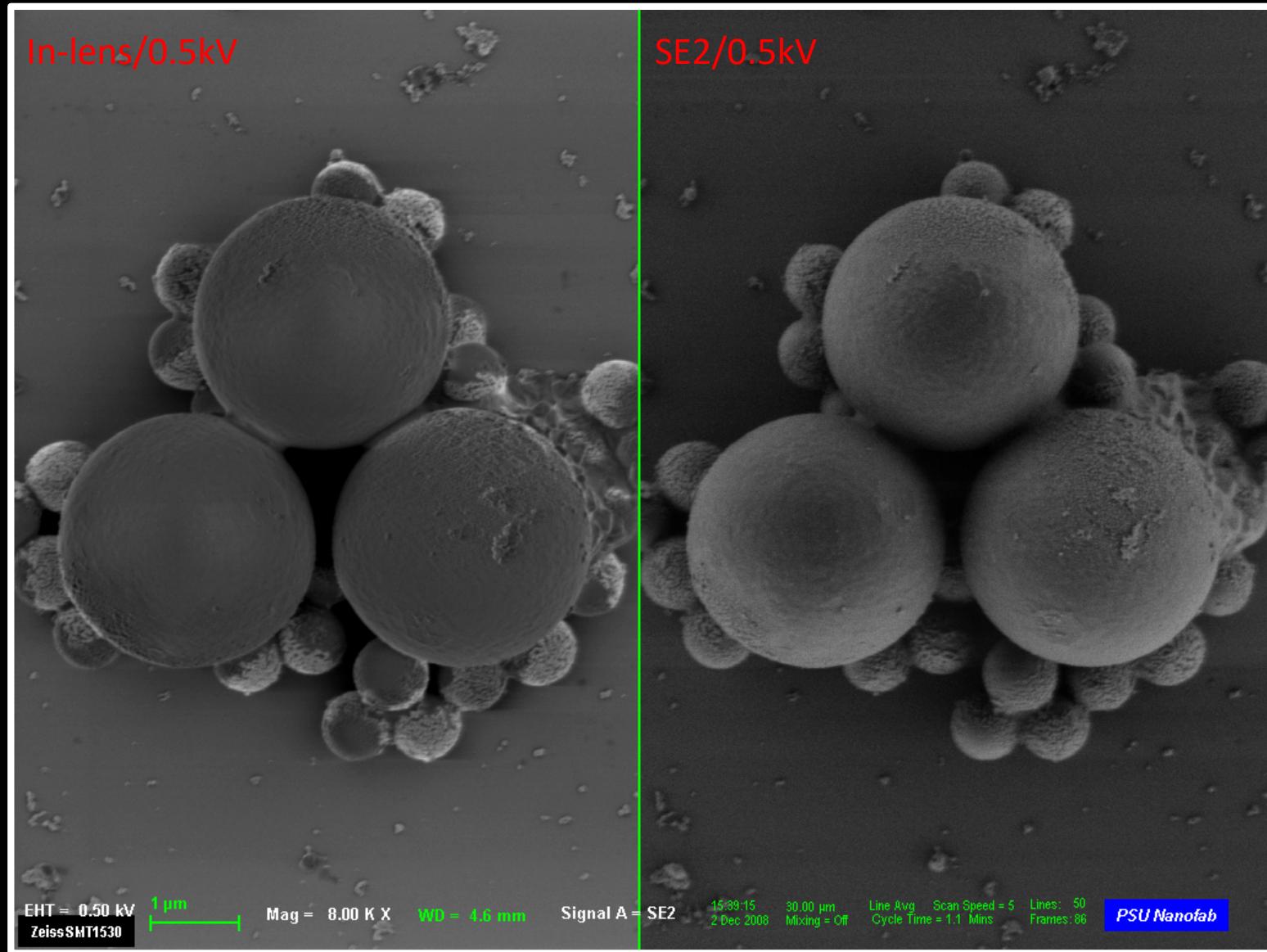
Smaller WD, better resolution

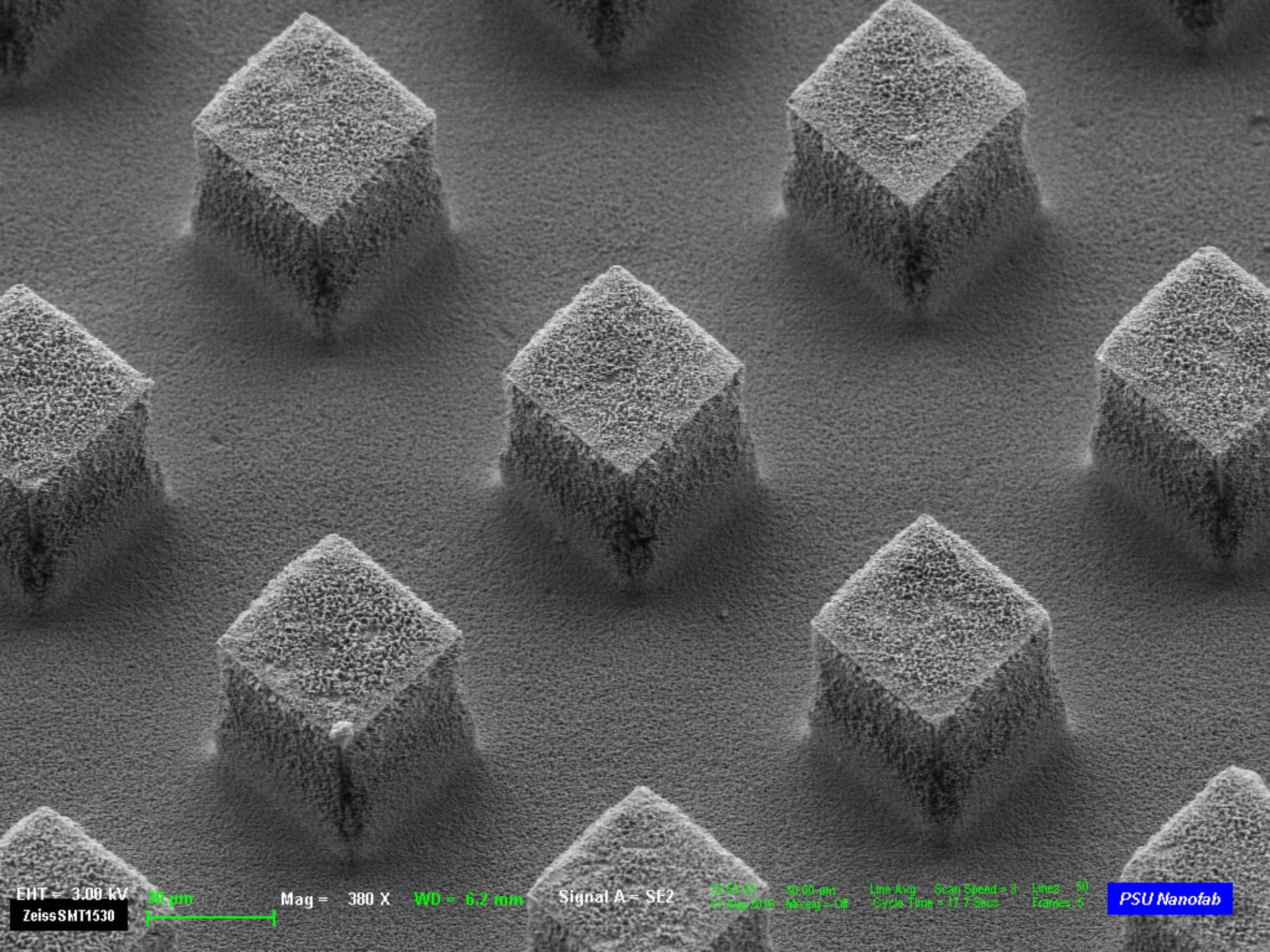


Working distance & detectors



Choice of detectors





EHT = 3.00 kV
Zeiss SMT1530

30 μm

Mag = 380 X WD = 6.2 mm

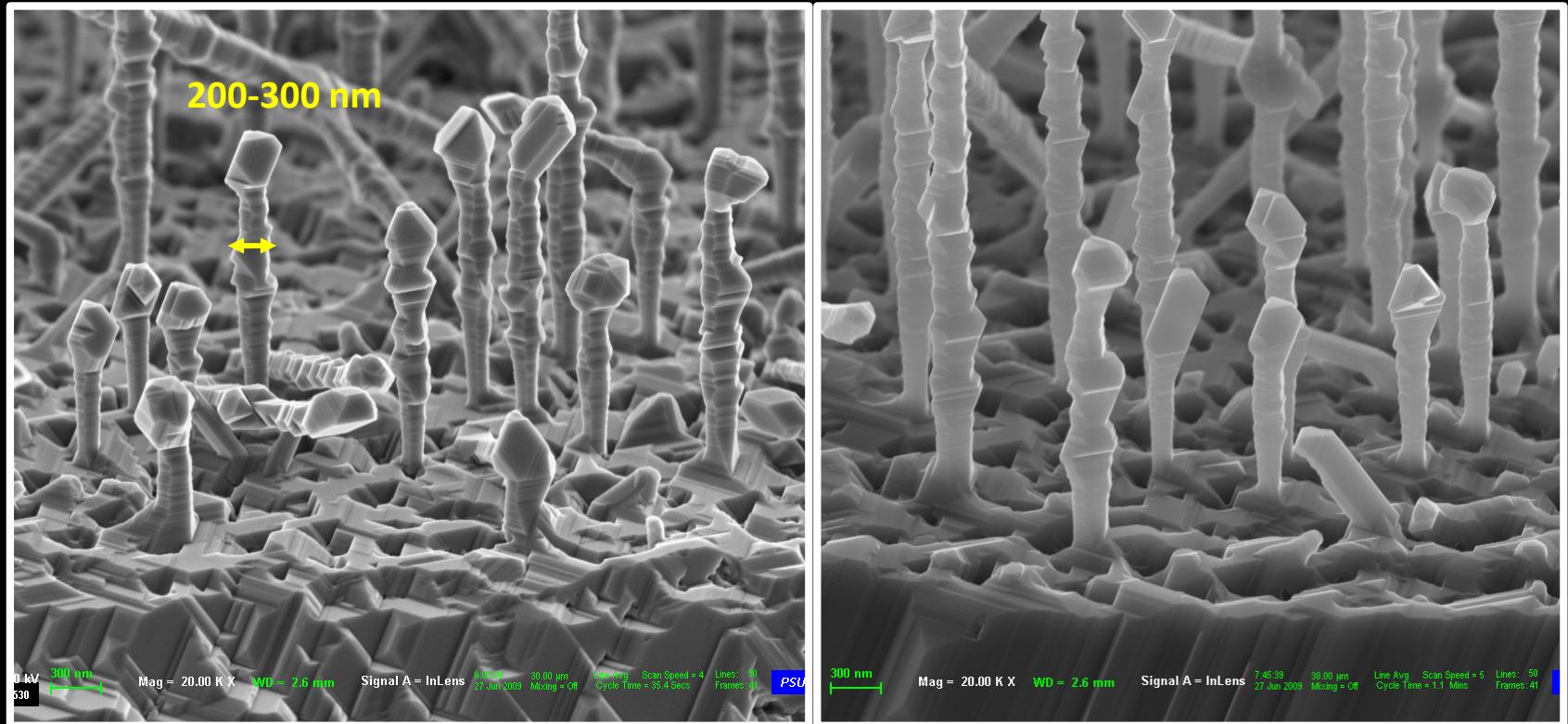
Signal A = SE2

22:55:23
11 Aug 2015
Milling = Off

50.00 μm
Line Avg Scan Speed = 1.7 Secs Lines: 50
Frames: 5

PSU Nanofab

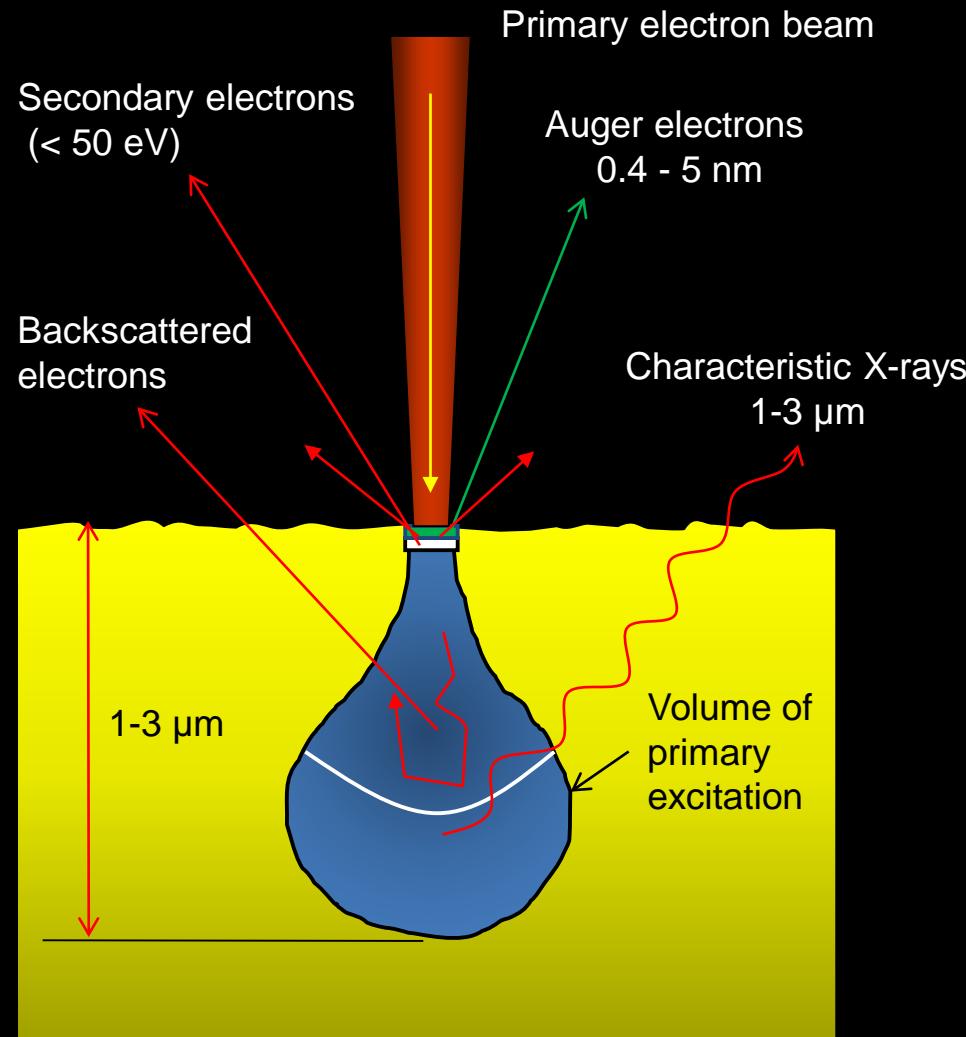
Choice of beam voltage



2kV/2.6mm

5kV/2.6mm

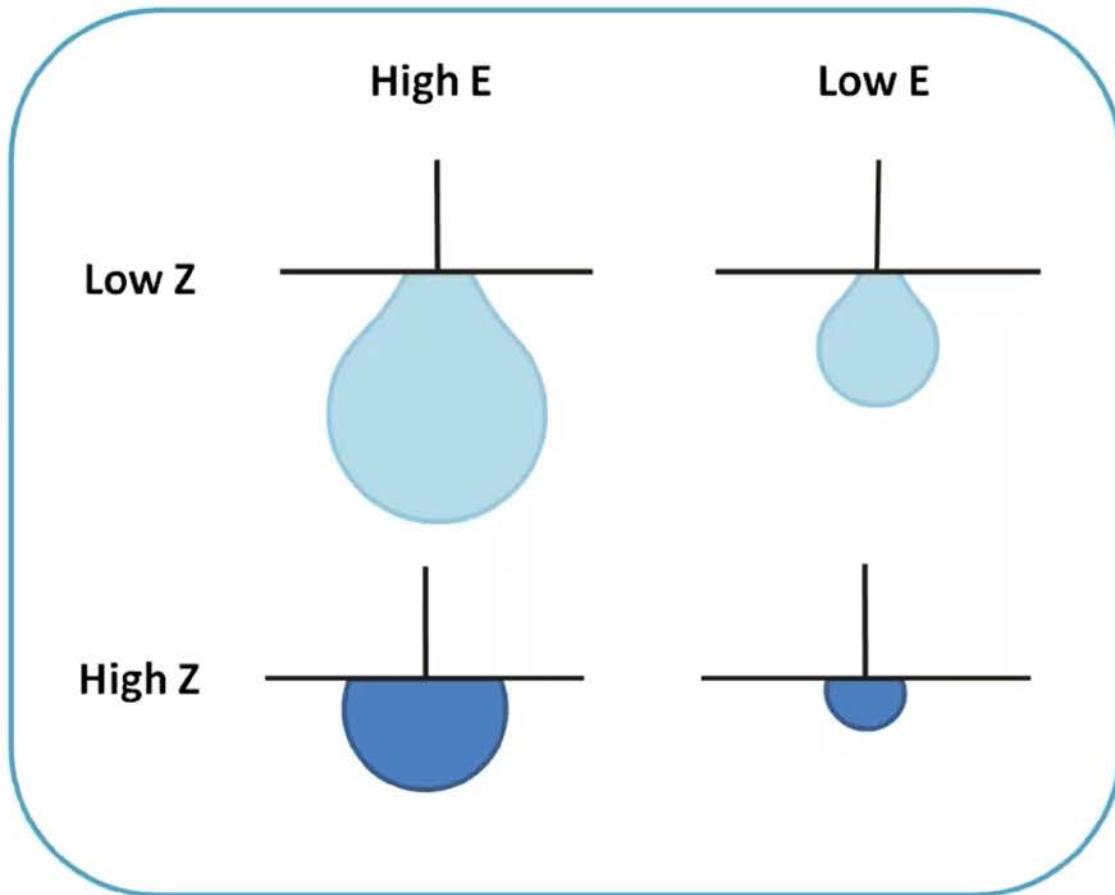
Electron and sample interaction



Electron – sample interaction volume

The size and shape of interaction volume depend on:

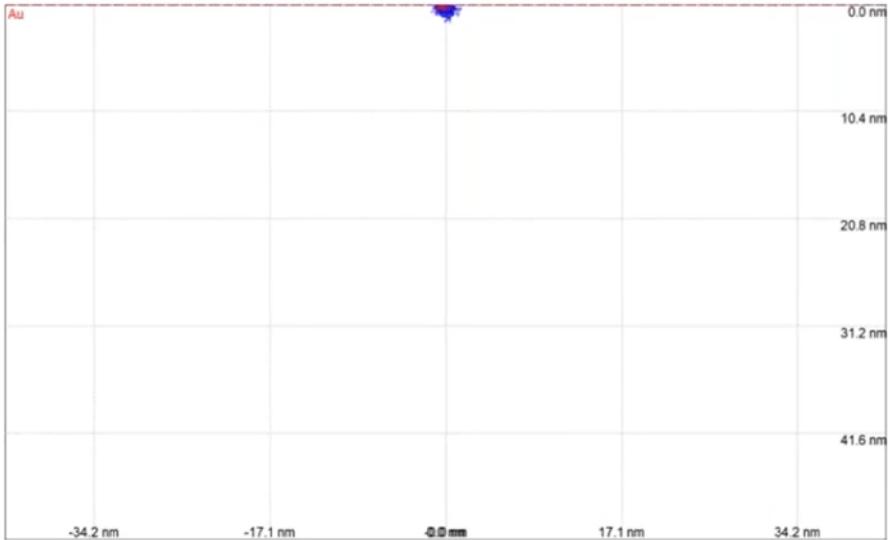
- Primary energy
- Atomic number (Z)
- Specimen tilt



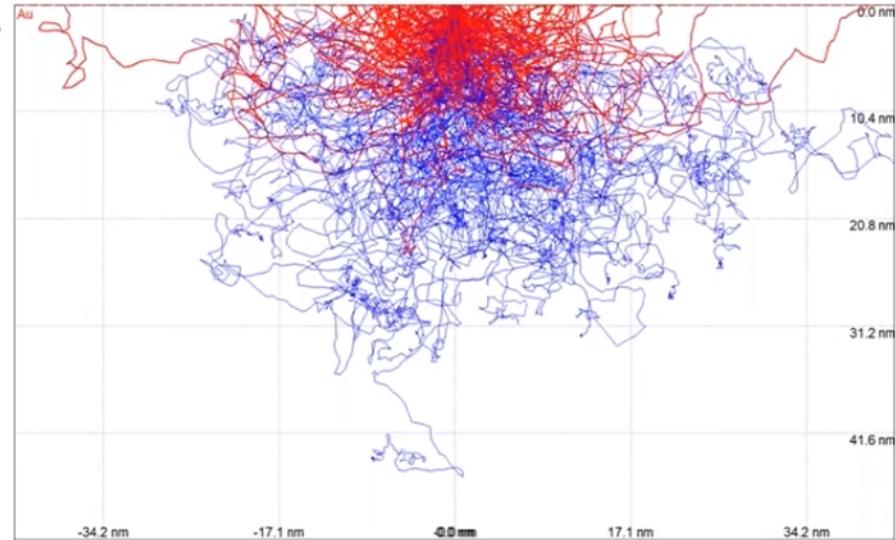
Low-voltage SEM

Example: Au

0.5 keV



5 keV



Advantages of low-voltage SEM:

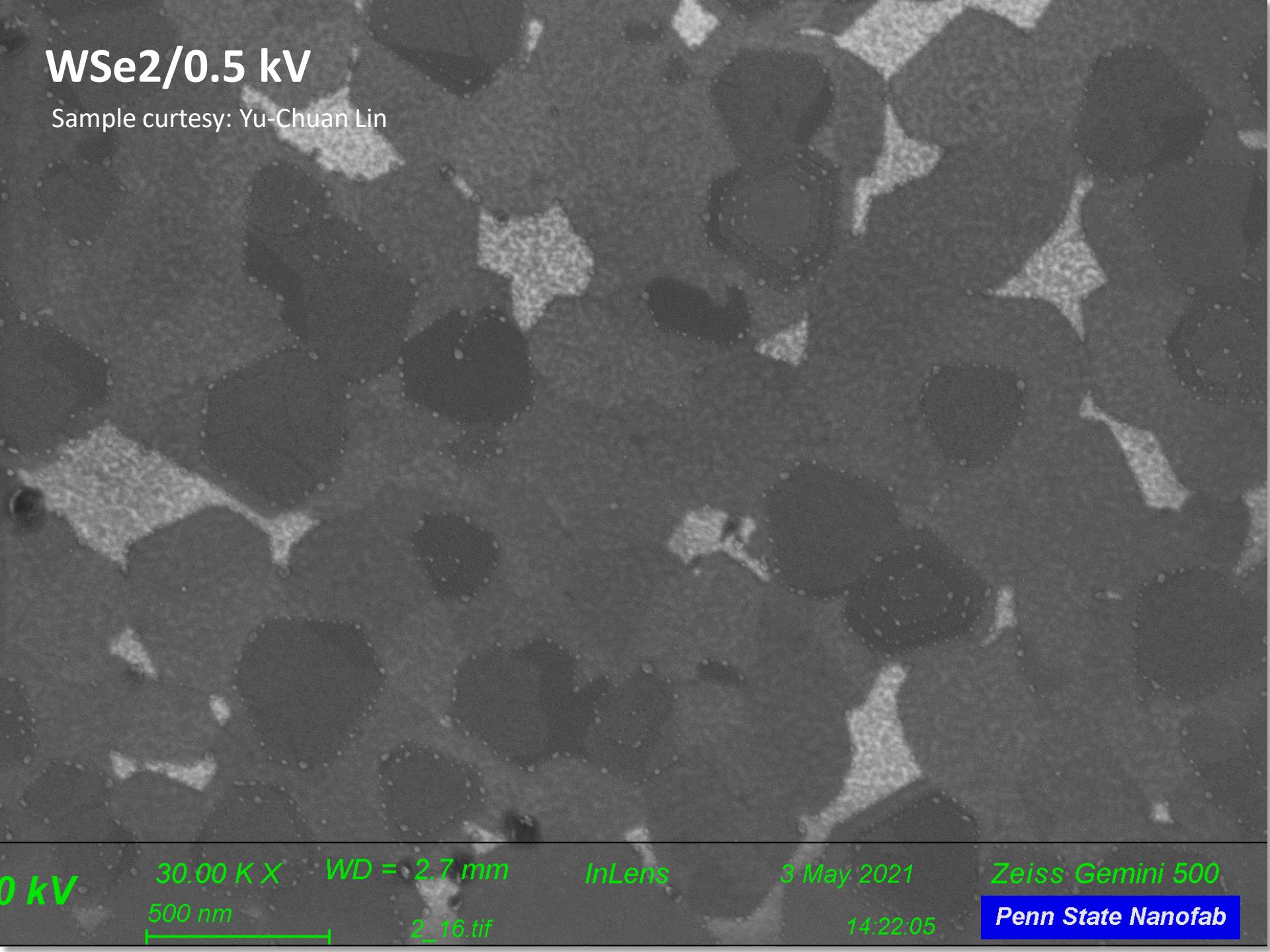
- Surface sensitive information
- Imaging of non-conductive specimens
- Imaging of beam sensitive materials
- Similar interaction volume for SE and BSE
- Increased spatial resolution

Contrast mechanisms:

- Topography
- Compositional contrast
- Channeling contrast
- Thin film contrast
- Magnetic domain contrast

WSe₂/0.5 kV

Sample courtesy: Yu-Chuan Lin



0 kV

30.00 K X

WD = 2.7 mm

InLens

3 May 2021

Zeiss Gemini 500

500 nm

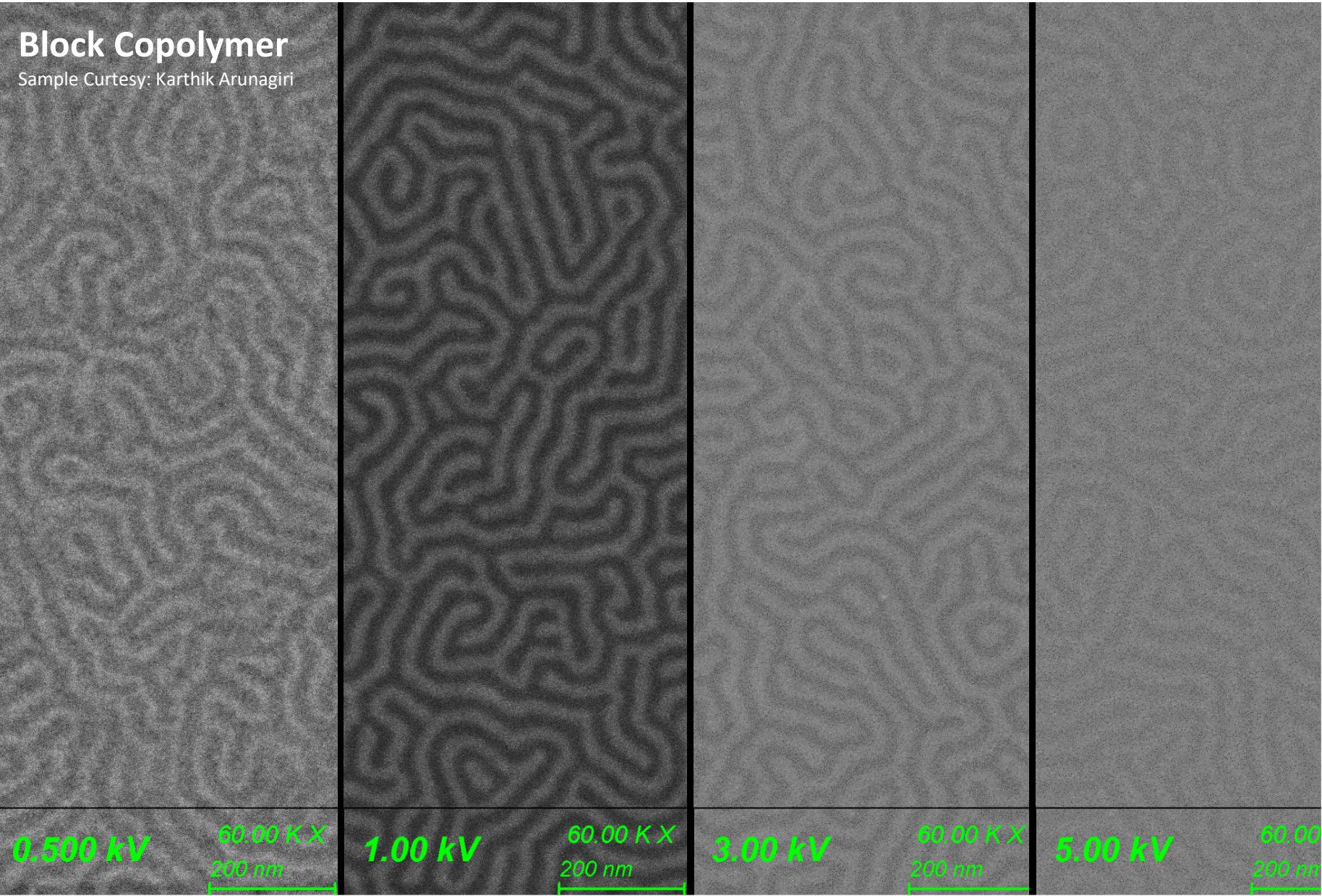
2_16.tif

14:22:05

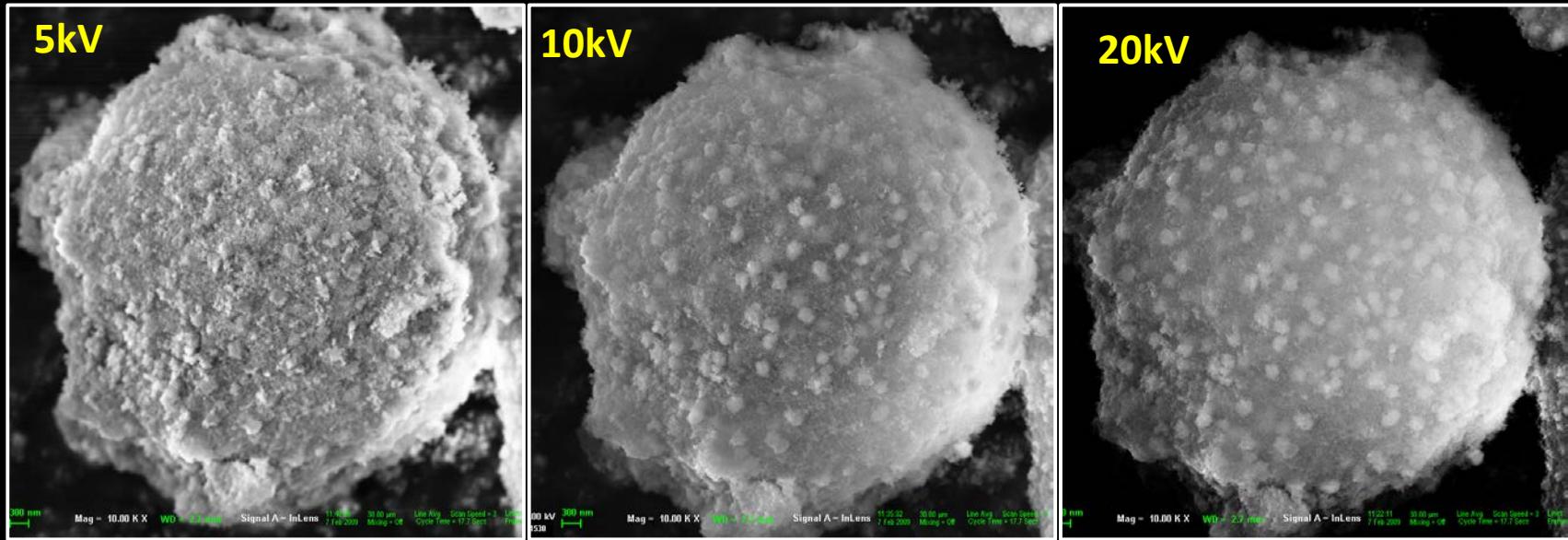
Penn State Nanofab

Block Copolymer

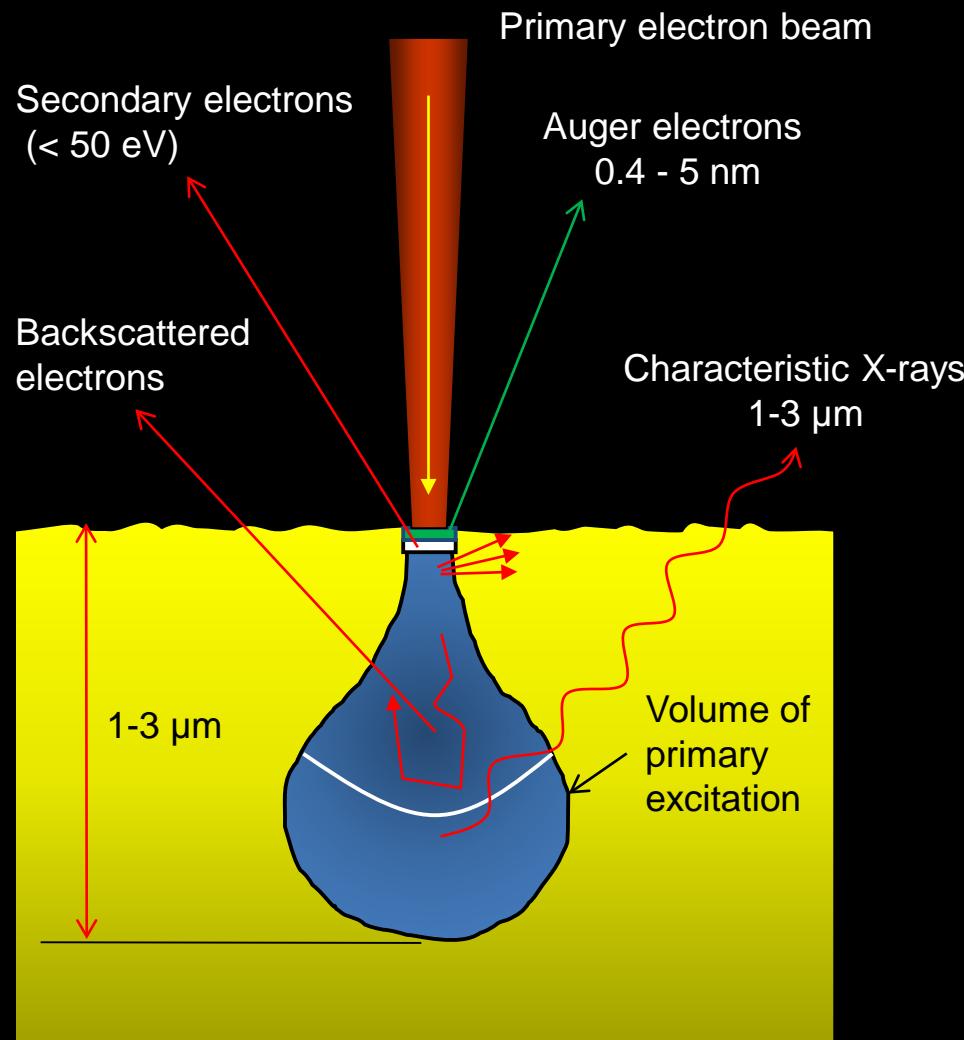
Sample Courtesy: Karthik Arunagiri



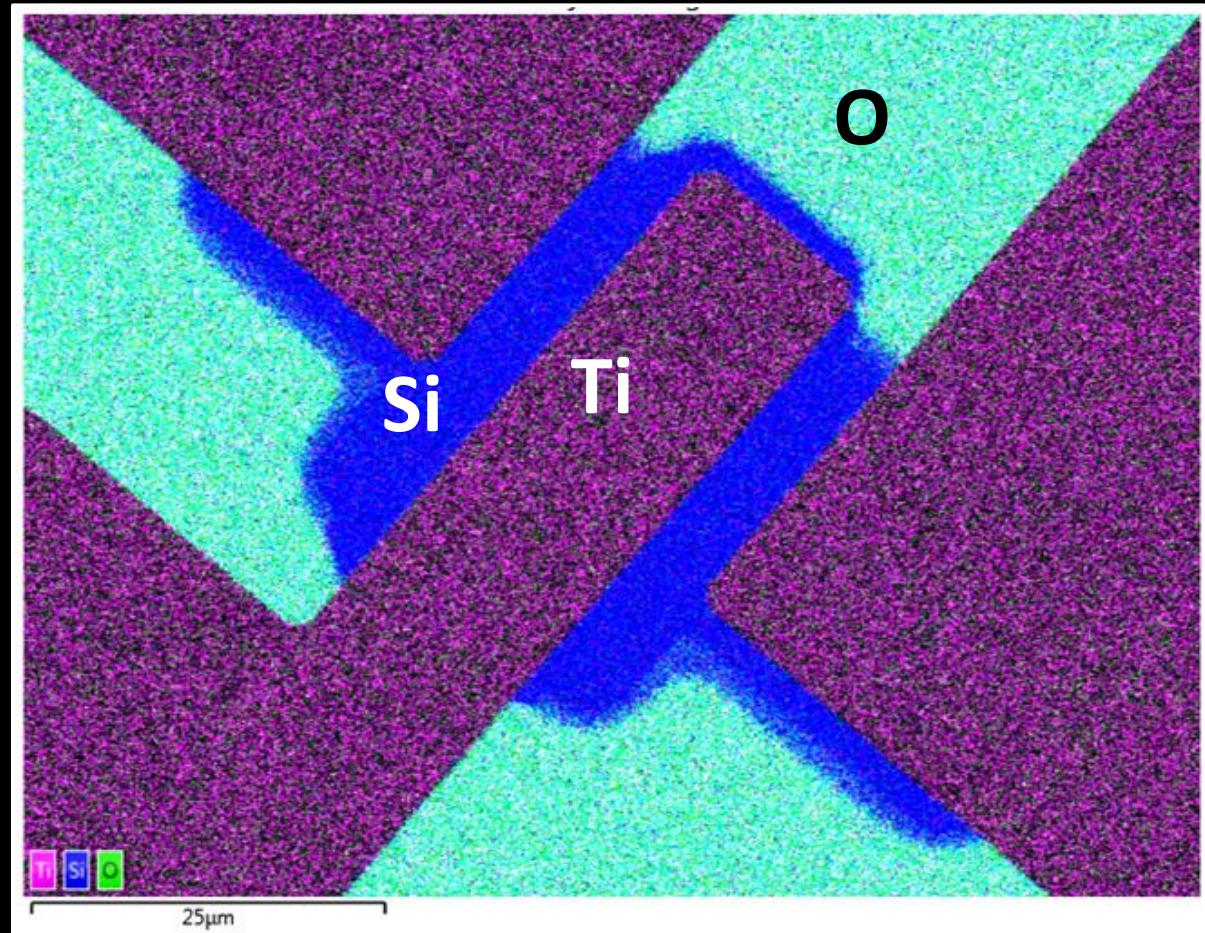
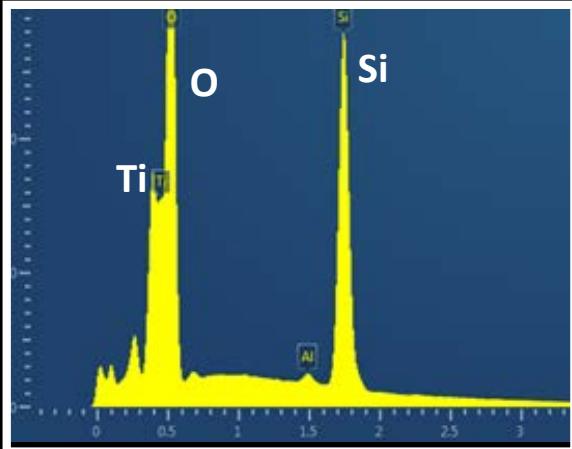
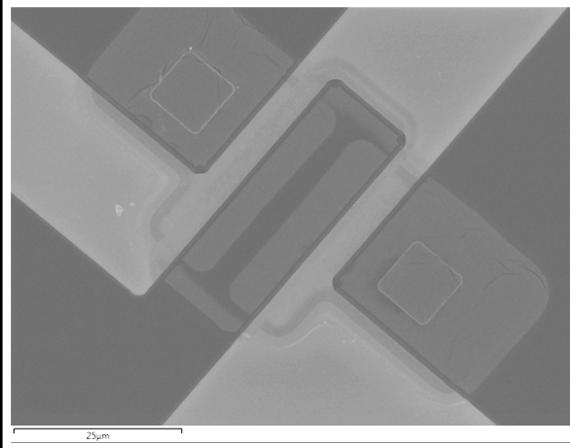
20% Ce on Al₂O₃ particle



X-ray emission & EDS



Device EDS Mapping



Outline

- Examples of different situations
- Key Imaging Parameters
- **FESEMs we own**
- How to achieve ideal beam

MERLIN

- HIGH BEAM CURRENT HIGH RESOLUTION
- EXTREME LARGE FIELD OF VIEW (6X4MM)
- HIGH SPATIAL RESOLUTION EDS
- LARGE AREA EDS MAPPING
- FAST SAMPLE TRANSFER (3" LOAD LOCK)



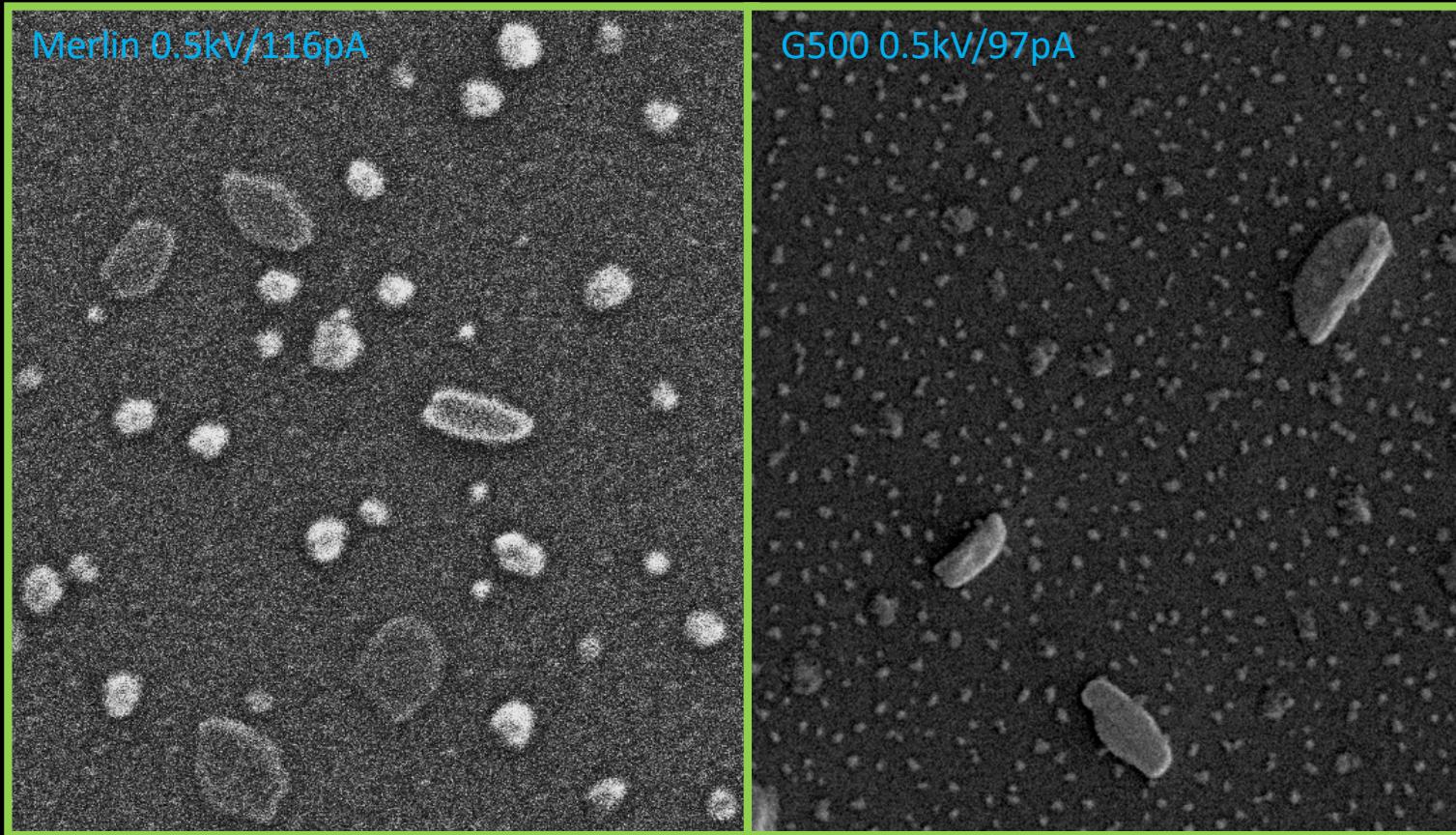
G500

- LOW KV HIGH RESOLUTION
- VP FOR INSULATING MATERIALS
- CATHODOLUMINESCENCE IMAGING
- IN SITU PLASMA CLEANING
- FAST SAMPLE TRANSFER (3" INCH)



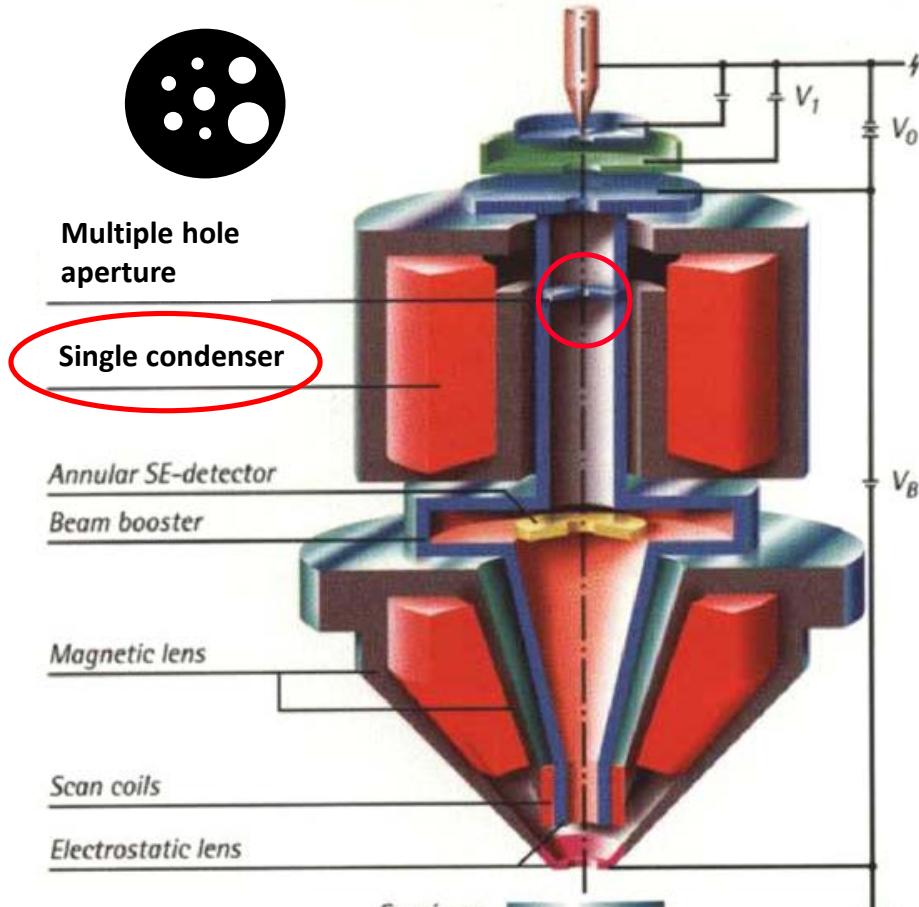
G500: Excellent resolution at low KV

2D sample 2: MoS₂ on glass



Low KV minimizes beam damage and the high resolution allows us to see the small features, in this case, nm size nucleation sites, which are barely visible on the left image taken on Merlin.

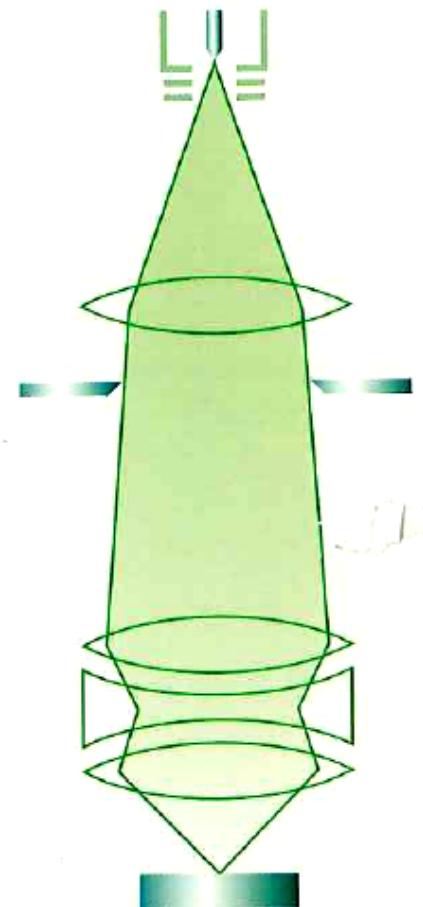
GEMINI I column (G500)



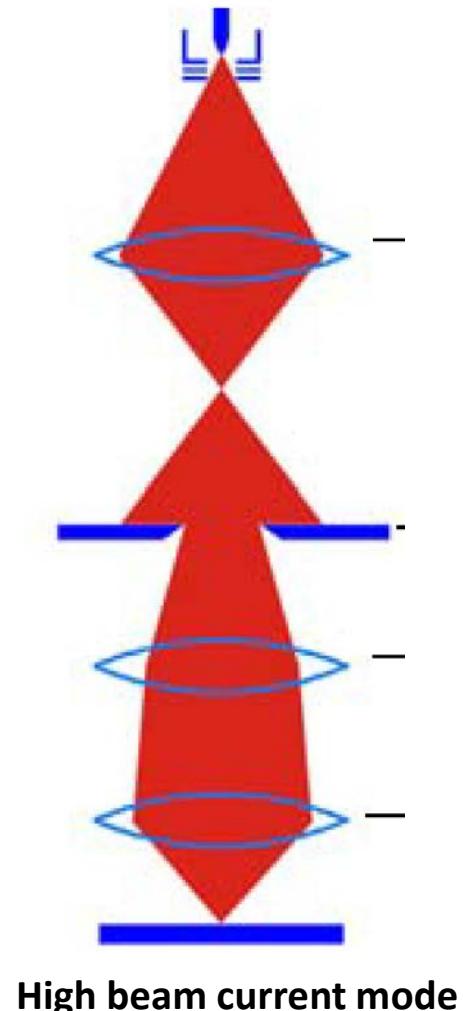
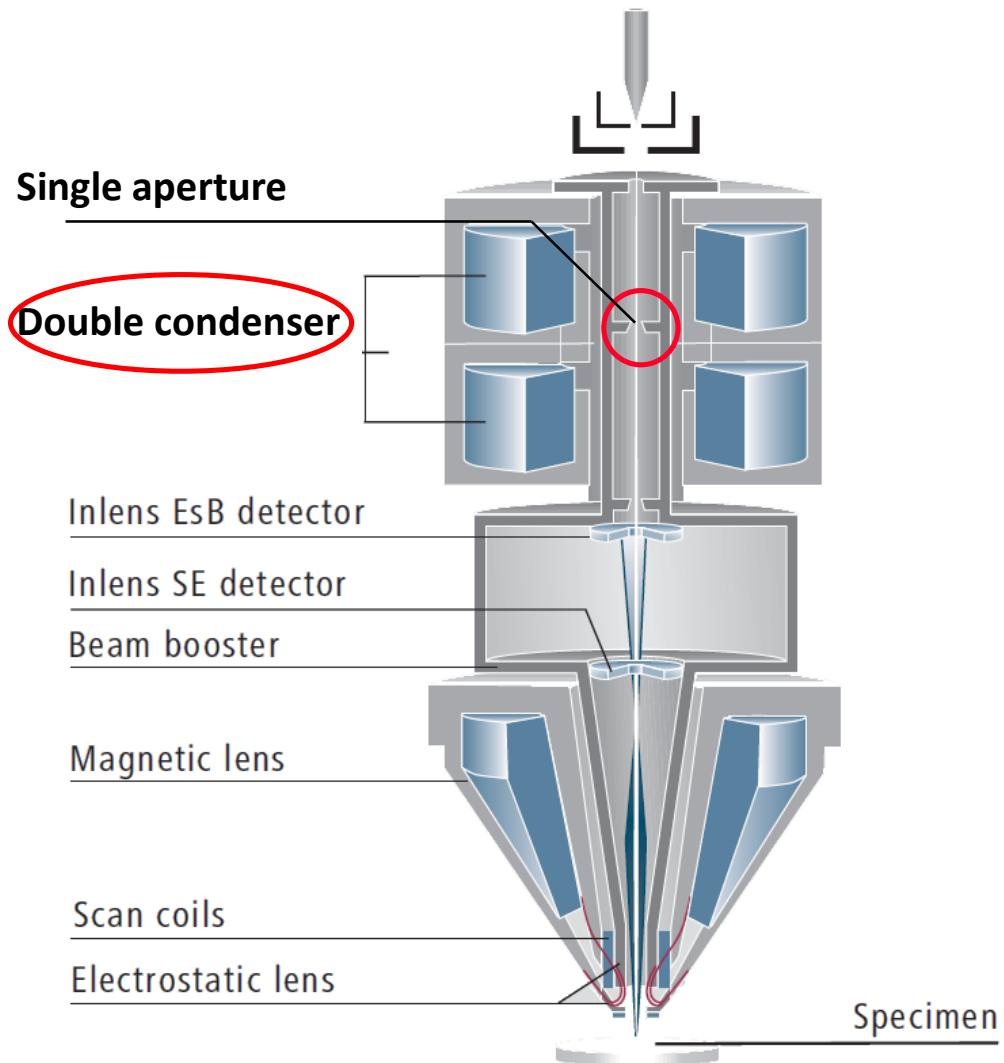
V_1 – extractor voltage at first anode

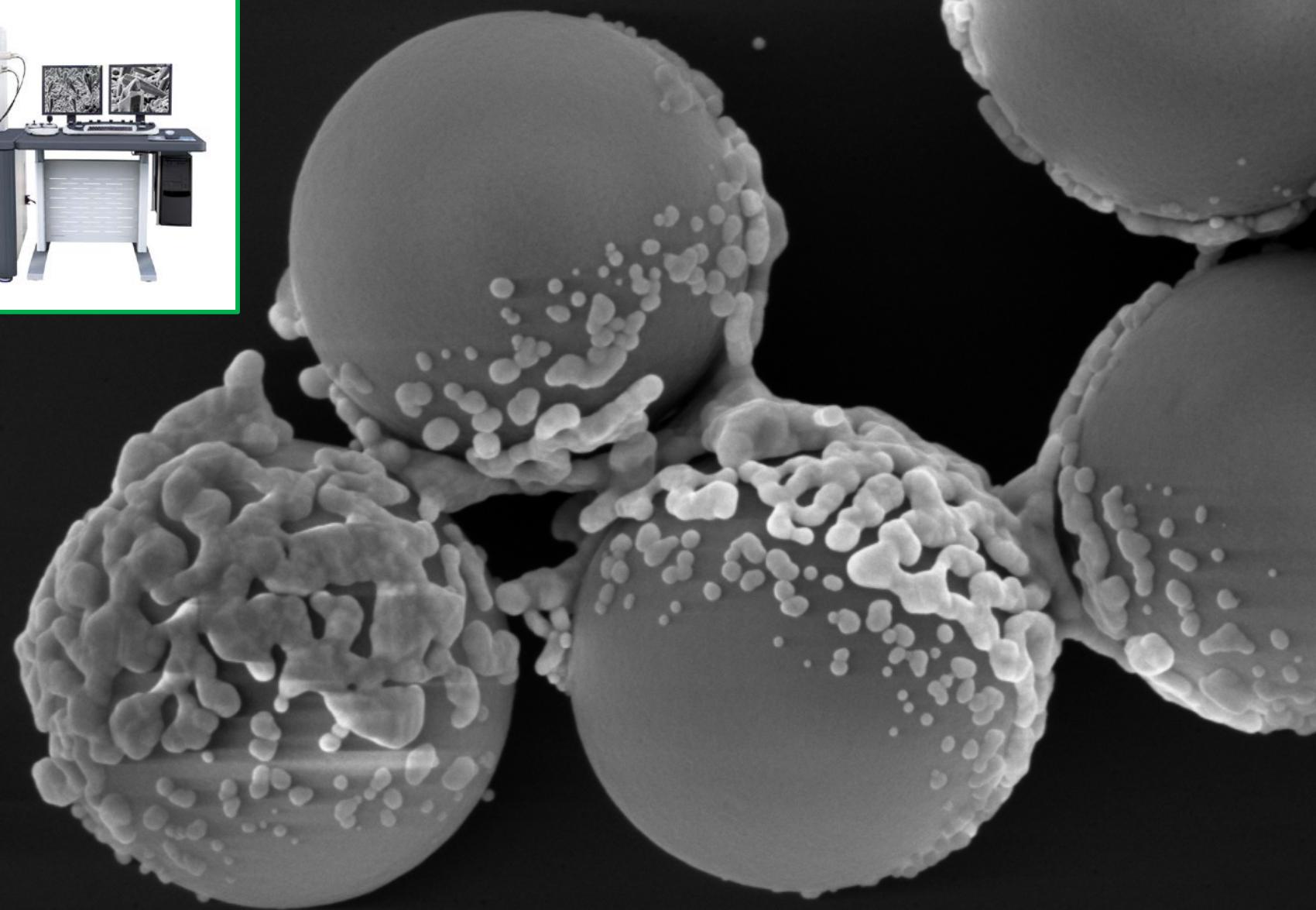
V_0 – accelerator voltage at second anode

V_B – booster voltage



GEMINI II column (Merlin)





Ultra 55 CNEU owned 7/12/2010

Mag = 51.57 K X 100 nm
ULTRA 55-36-76

WD = 1.8 mm

EHT = 5.00 kV
Noise Reduction = Line Avg

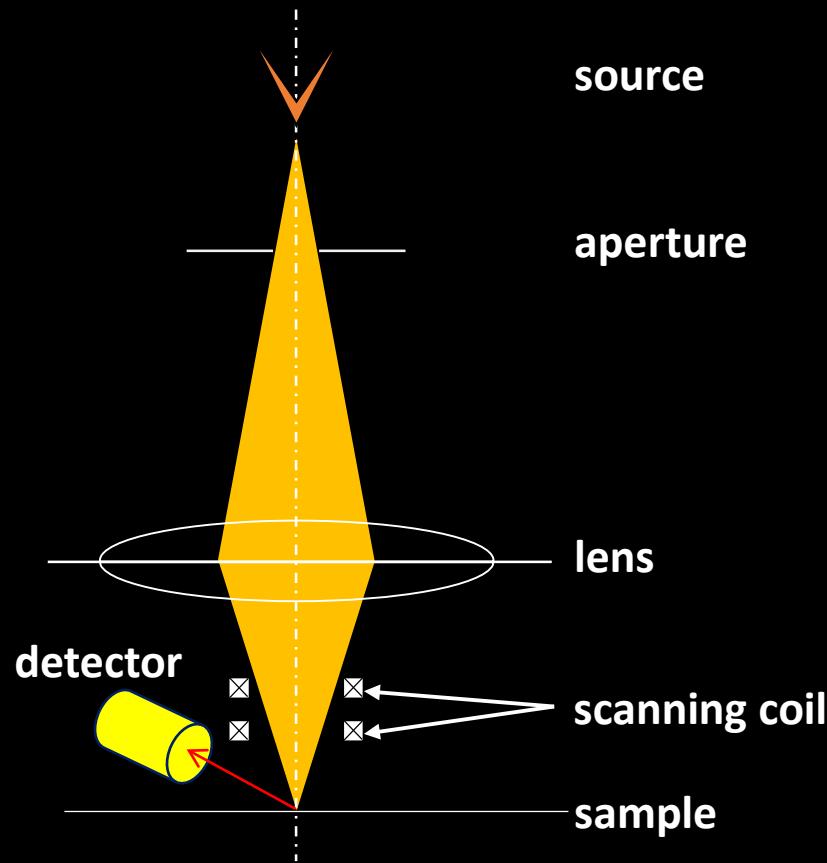
Signal A = InLens
ESB Grid = 0 V

Time :17:38:43
Date :12 Jul 2010

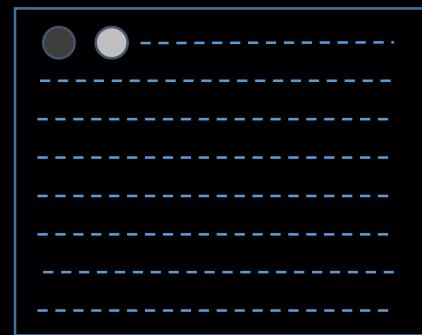
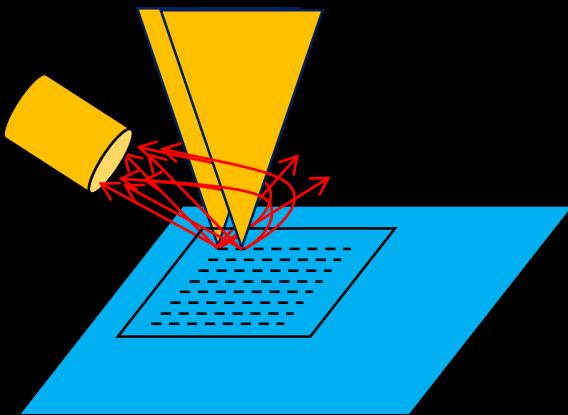
Outline

- Examples of different situations
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- How to achieve ideal beam

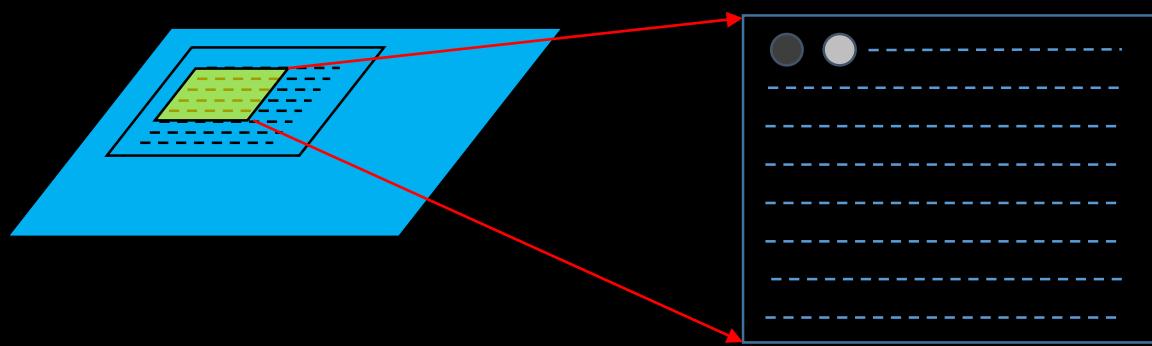
A simplified ray diagram of SEM



Scanning->move the beam!



Magnification?



Merlin: Large field of view

H 1 = 3.054 mm

V 1 = 4.075 mm

5.00 kV

28X
200 μ m

WD = 6.4 mm

SE2

3 May 2021

ESB Grid = 750 V

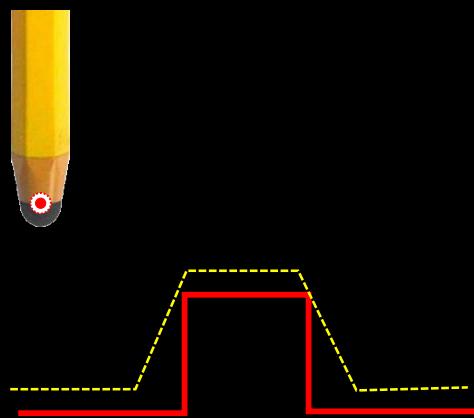
Tilt Angle = 10°

Zeiss Merlin

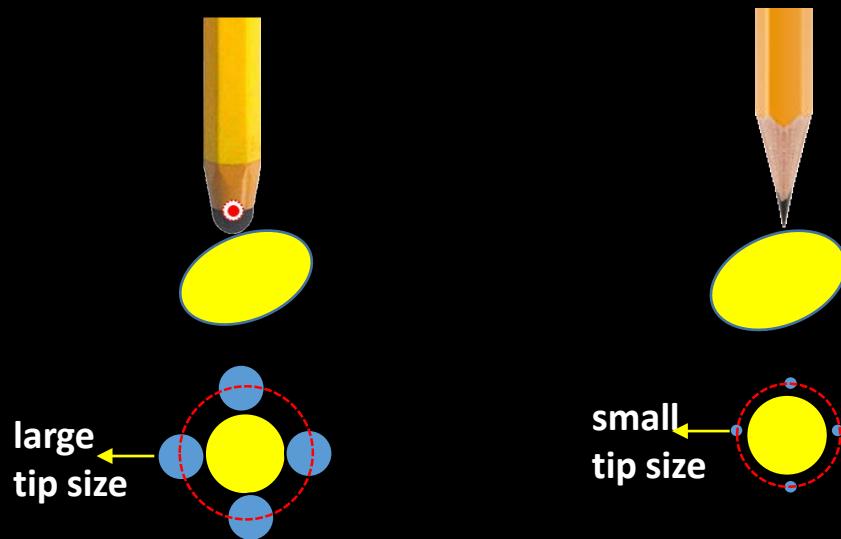
Penn State Nanofab

Ideal beam?

Electron beam is a probe, just like your pencil

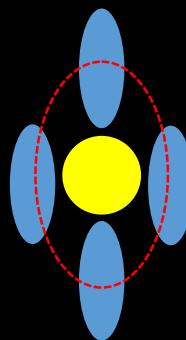
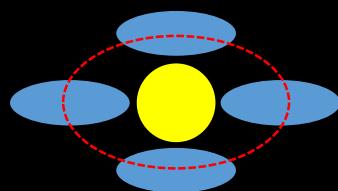


Tip size matters!

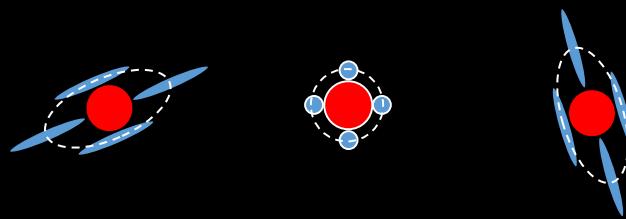
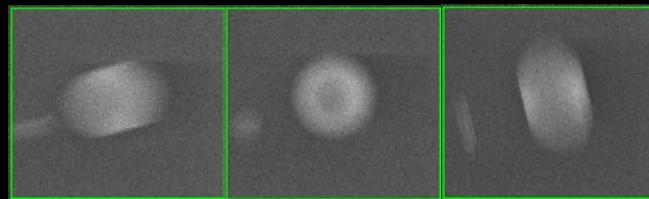


Smaller tip size → better resolution

Tip shape matters too!



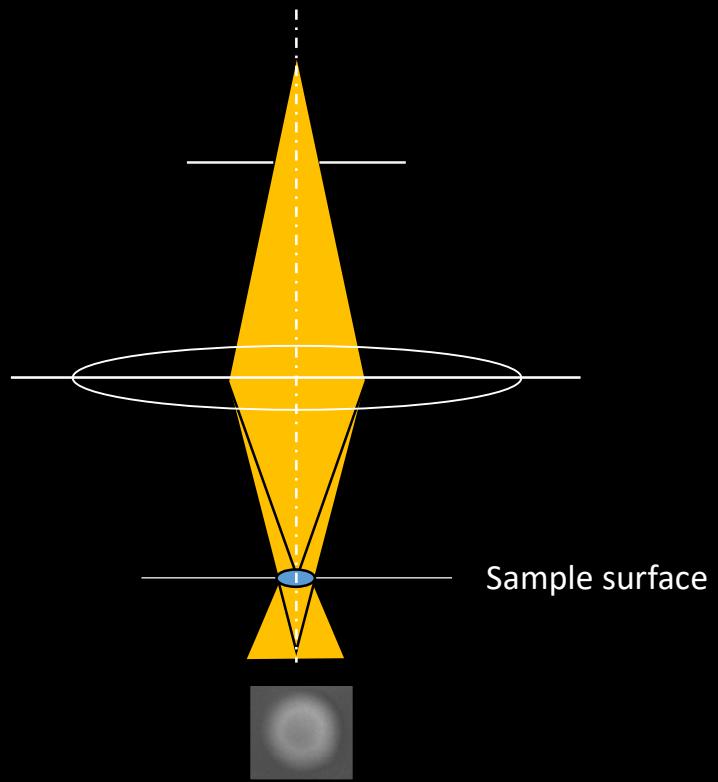
How does the beam shape affect SEM image?



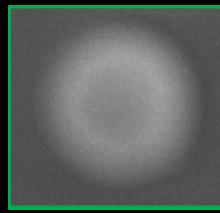
Ideal beam?

{ Small
Round
Straight

How to achieve sharp beam on FESEM?

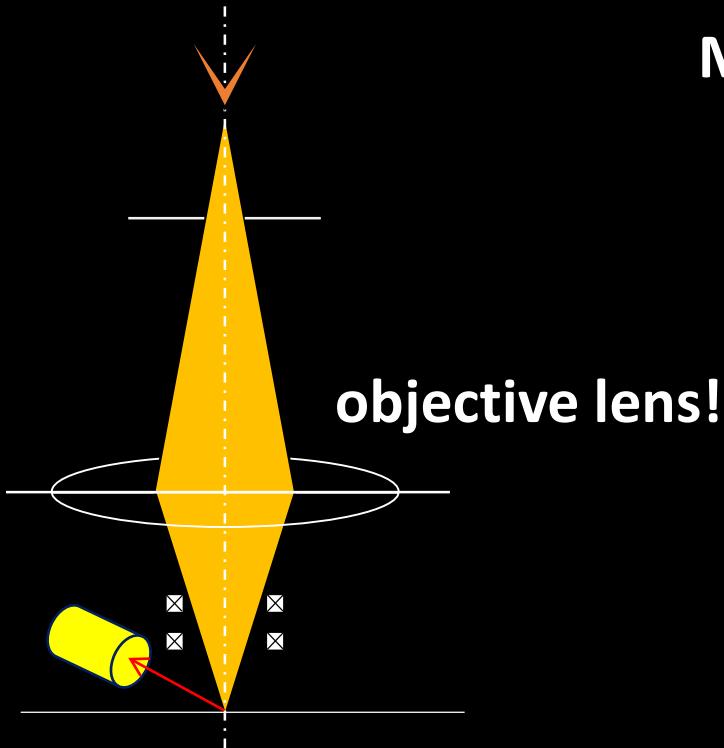


Varying focus changes beam size !

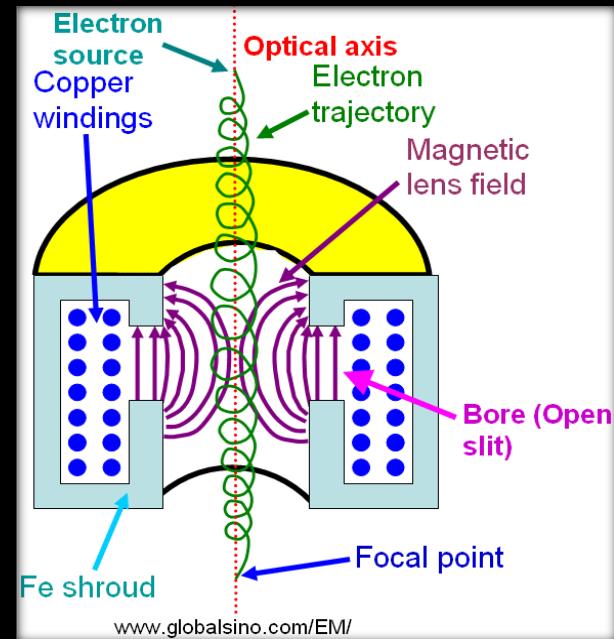


{ Small -> focus
 Round ?
 Straight

Which component control beam shape?



Magnetic lens or pole piece

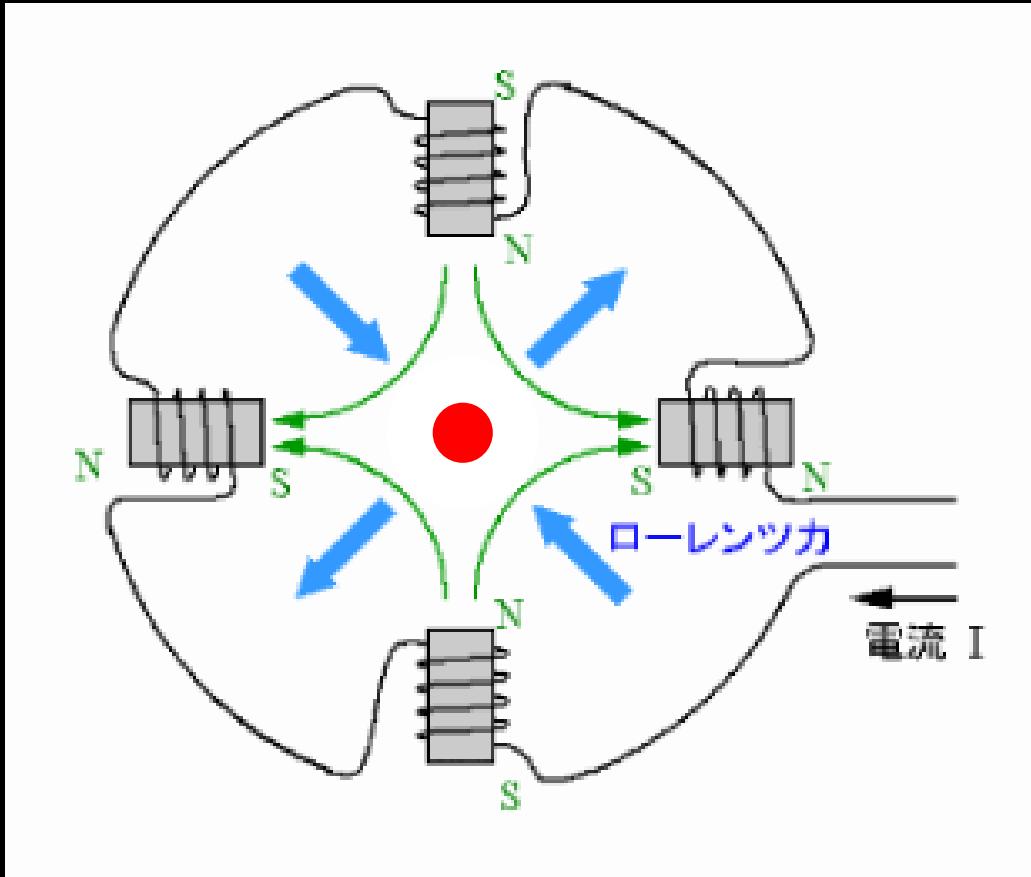


Field is not symmetrical -> lens is not round

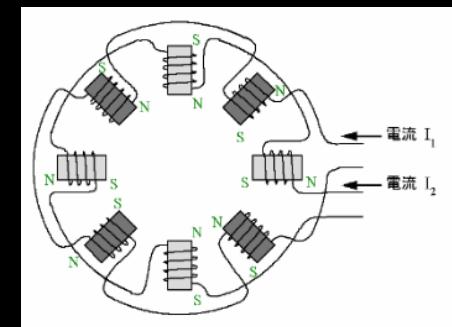
{ Small -> focus
 Round -> **Stigmatization/stigmatism**
 Straight

Mechanism to correct stigmation

Stigmators x/y



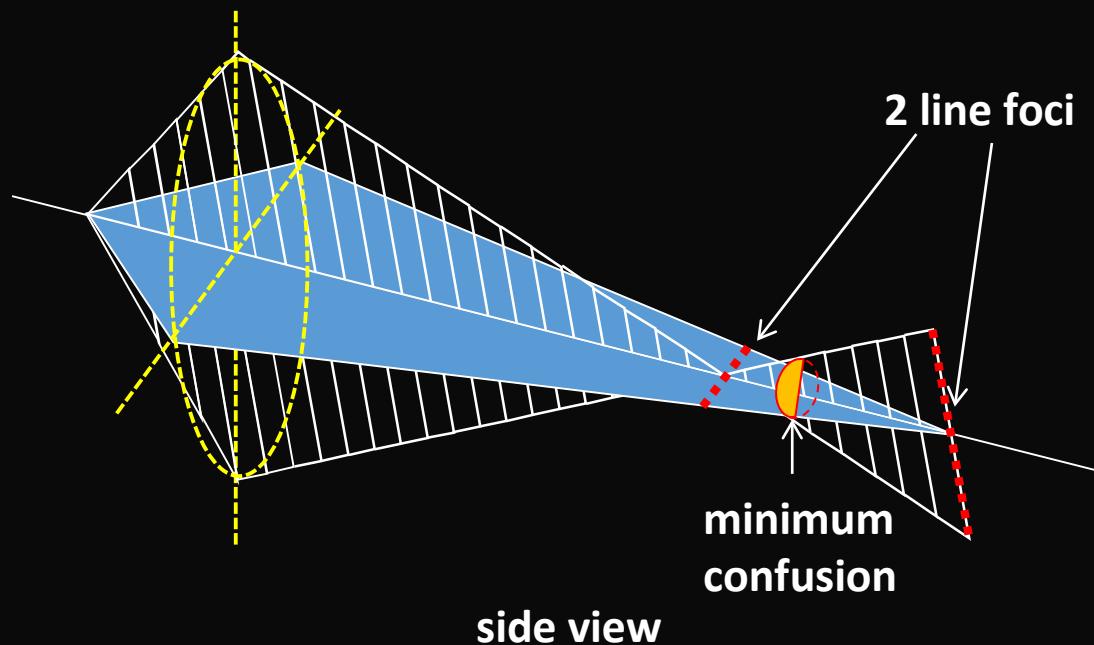
quadrupole stigmator

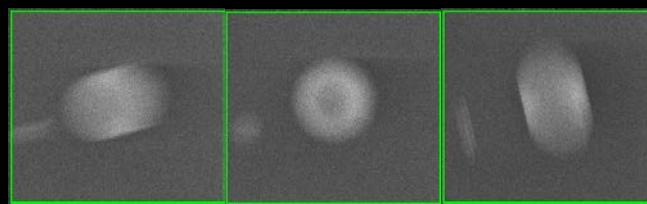
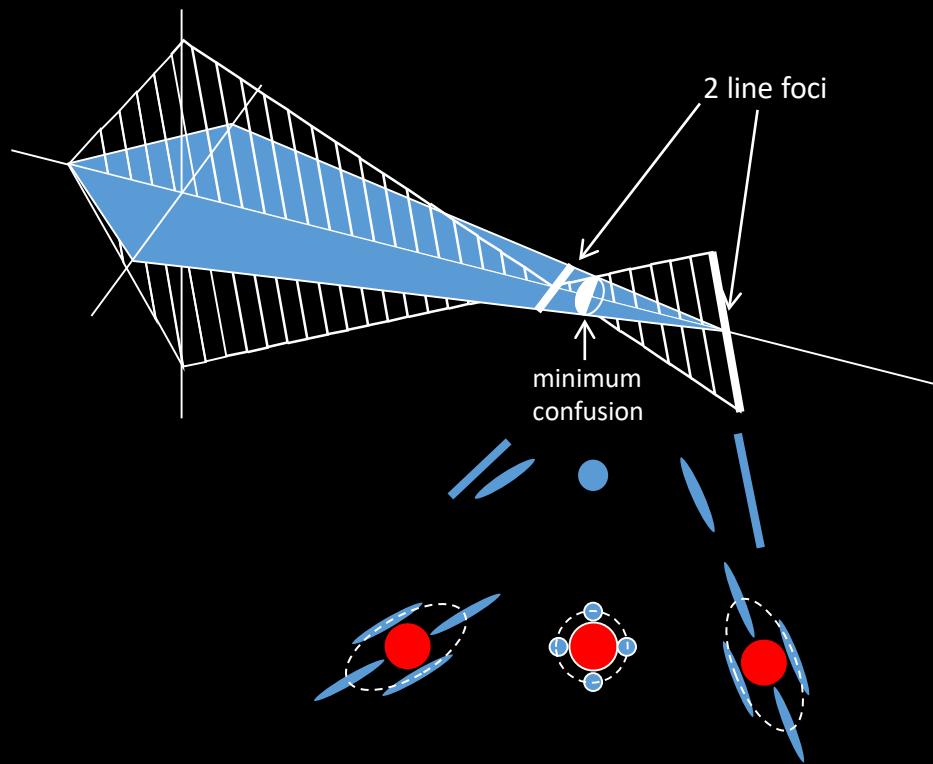


two sets of quadrupole

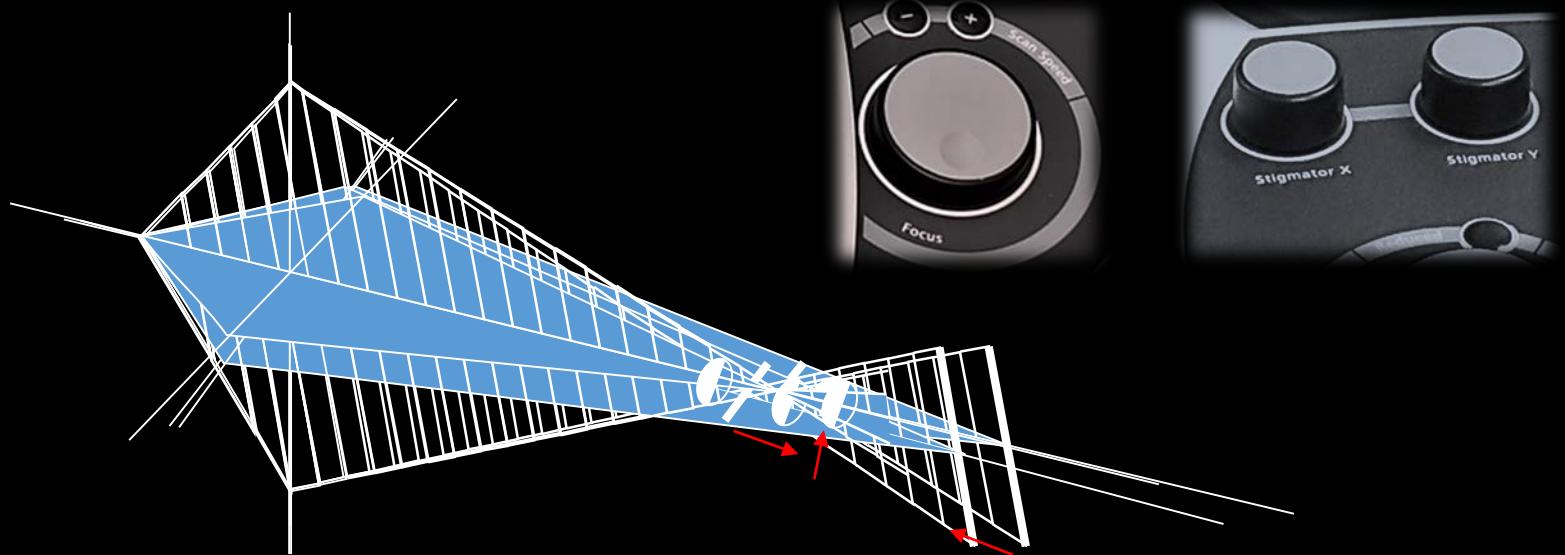
<https://www.jeol.co.jp/>

Ray diagram of a stigmatized lens





How to correct stigmation



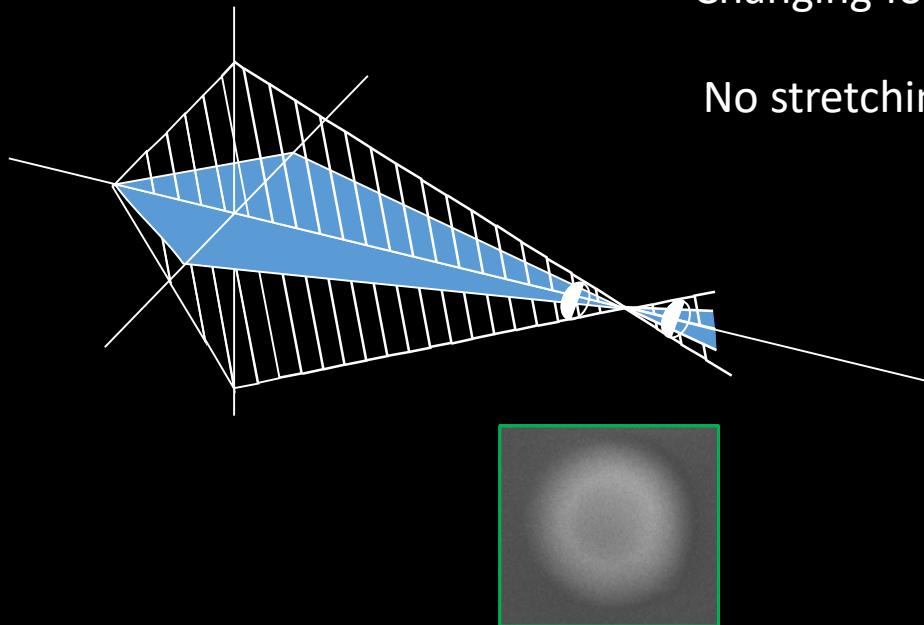
Repeating process:

Focus first -> x/y stigmation->focus again-> x/y ->focus->.....

How to test when stigmatism is corrected?

Changing focus again!

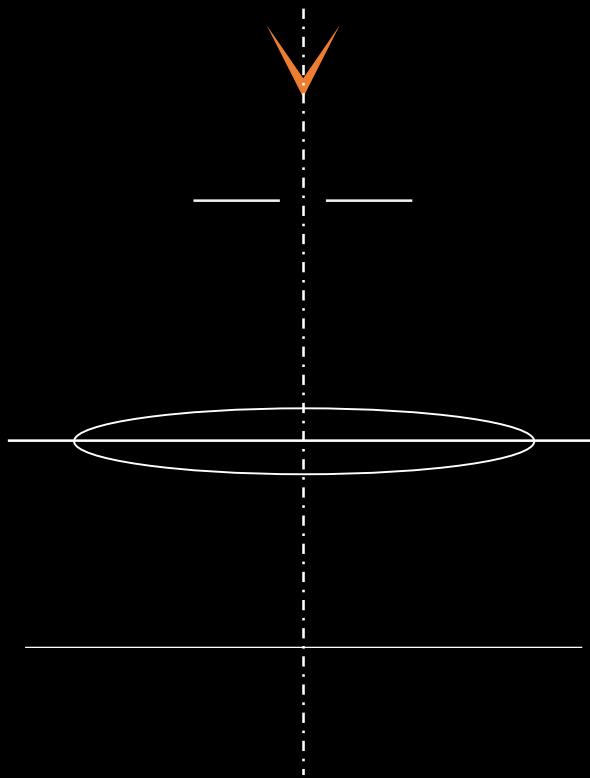
No stretching should be observed



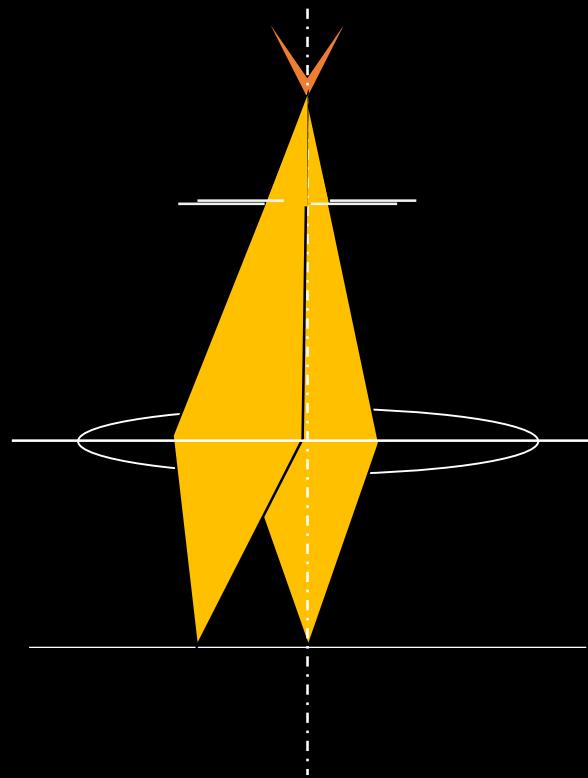
{ Small -> focus
 Round -> stigmatization
 Straight ?

Why straight beam?

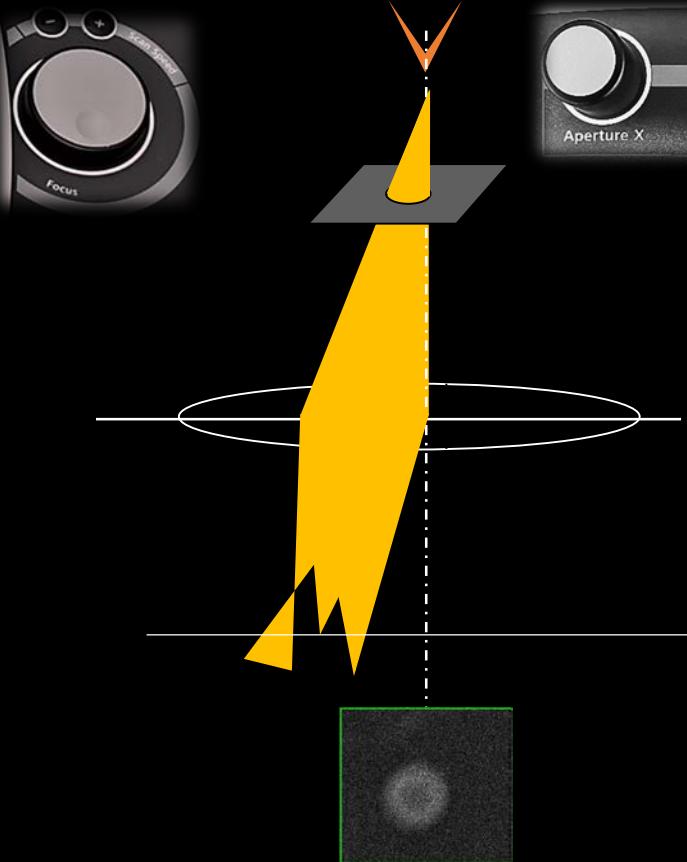
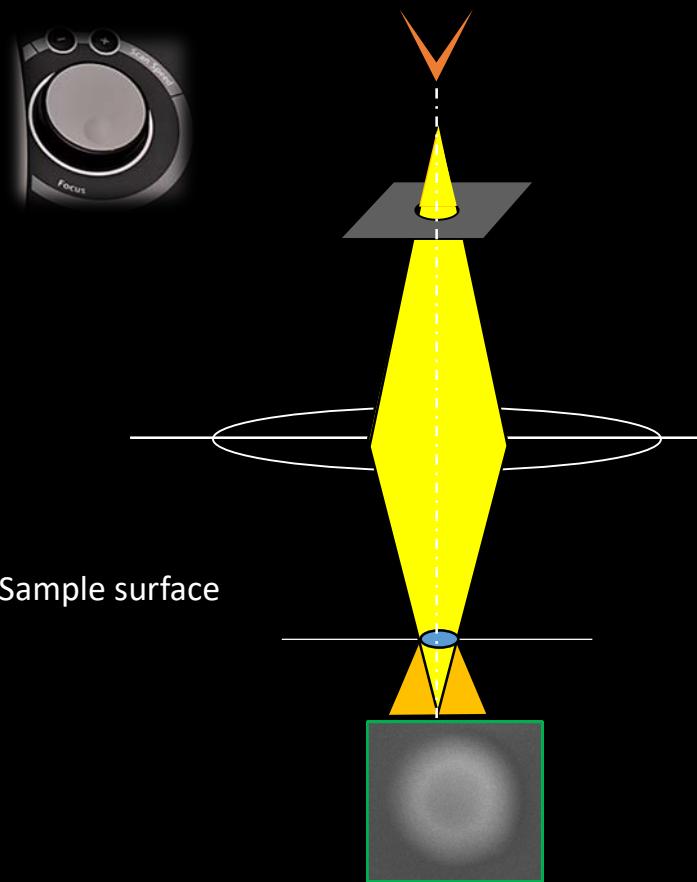
{ source
aperture
lens



What happens when aperture is off?

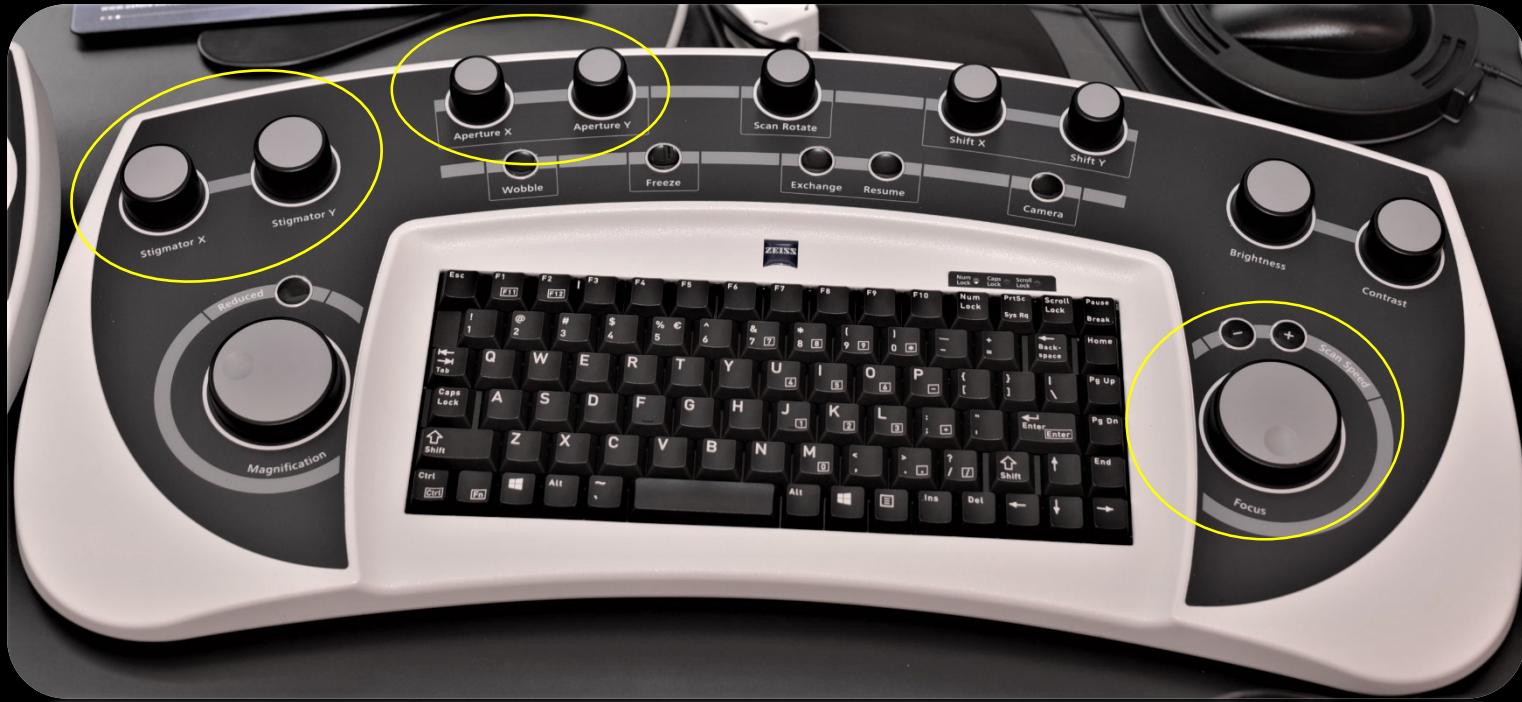


How do you know when aperture is off?



- 
- Small** -> focus
 - Round** -> x/y stigmatization
 - Straight** -> x/y alignment

5 controls needed to correct the beam



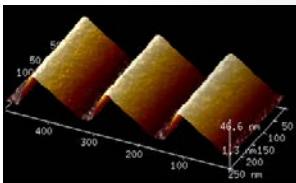
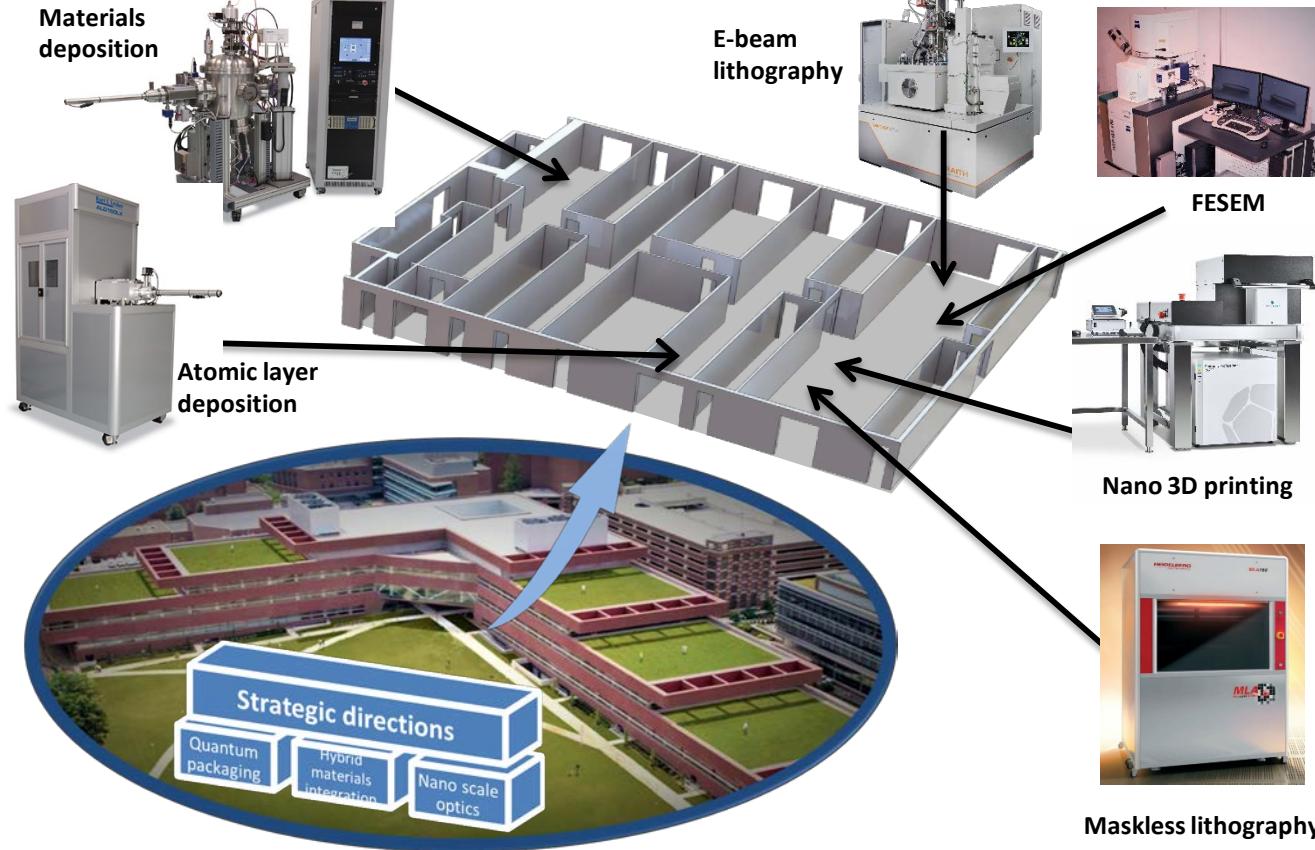


Questions?

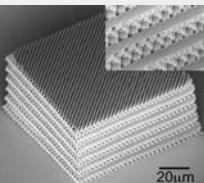


The Nanofabrication Lab: Enabling the future of nanoscale materials and devices at Penn State University

Chad Eichfeld, Guy Lavallee, Andrew Fitzgerald, Bangzhi Liu, Bill Mahoney,
Kathleen Gehoski, Ted Gehoski, Michael Labella, Wanlin Zhu, Shane Miller, Jaime Reish and Daniel Lopez



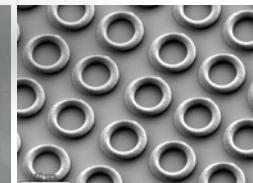
Reflection gratings for X-ray radiation



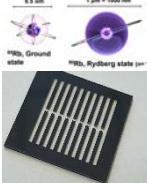
Photonic bandgap structures



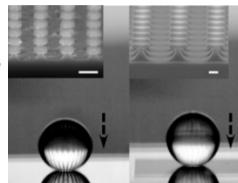
Nanostructured optics



Array of toroidal nanostructures



Atomic vapor cells



Nanostructured surfaces



Materials expertise:
Metals, semiconductors, dielectrics,
Van der Waals.

Lithography Suite:
Electron beam, ion beam, direct
write optical, stepper, and contact
lithography capabilities.

Deposition Suite:
Sputtering tools, electron beam
evaporation, atomic layer and
plasma-enhanced chemical vapor
deposition.

Etching Suite:
Plasma, high density plasma, and
deep reactive ion etching of
dielectrics and metals.

Metrology Suite:
SEM, profilometers, spectroscopic
ellipsometry and atomic force
microscope.

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2D Crystal Consortium
NSF Materials Innovation Platform